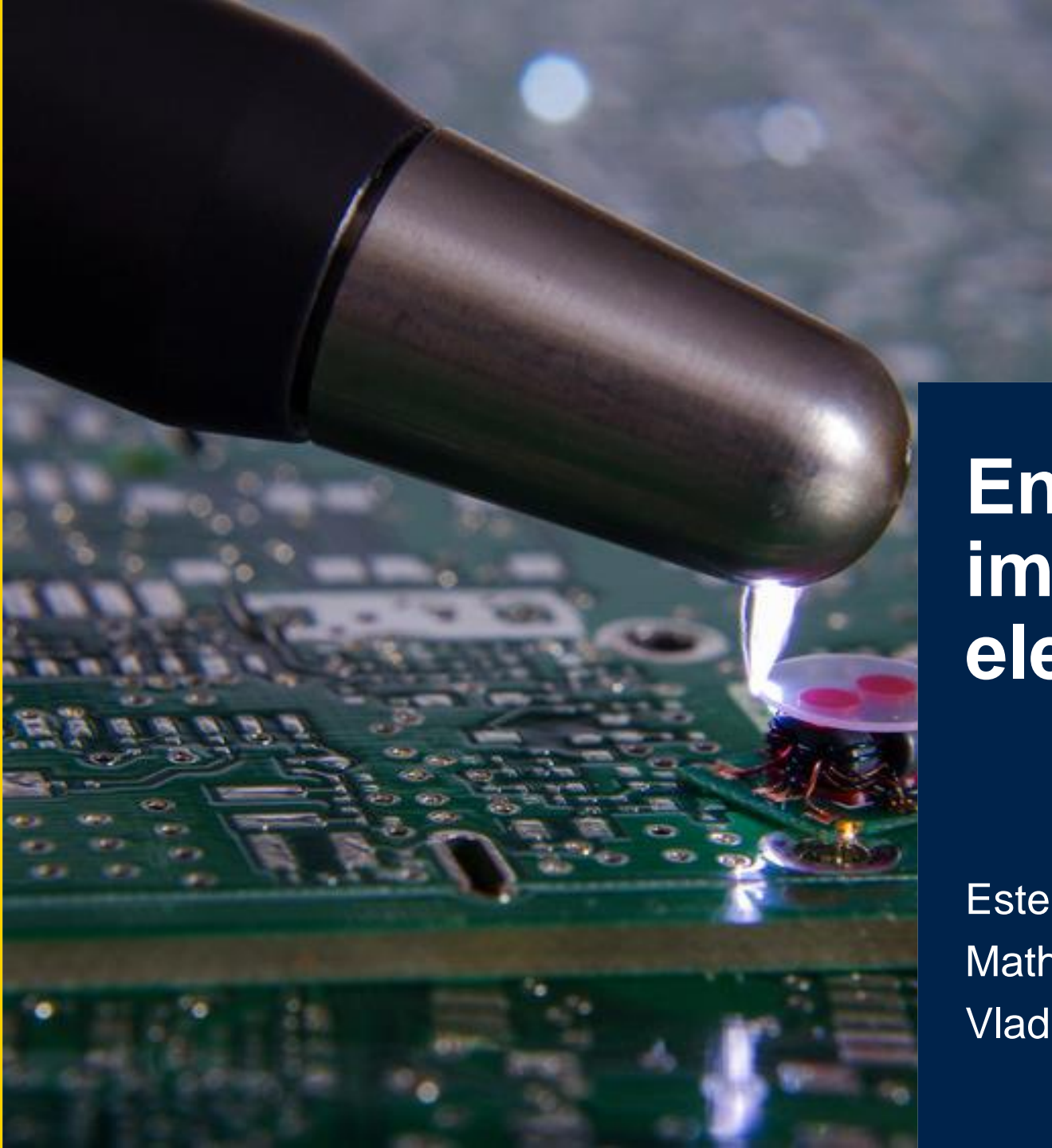




life.augmented

A close-up photograph of a soldering iron tip touching a component on a green printed circuit board (PCB). The iron is dark and metallic, and a small amount of solder is visible at the point of contact. The background is blurred, showing other components on the board.

Ensuring system immunity against electrostatic discharges

Estelle ASTAR, Product Marketing Engineer
Mathieu ROUVIERE, Application Engineer
Vladimir JANOUSEK, Application Team Manager

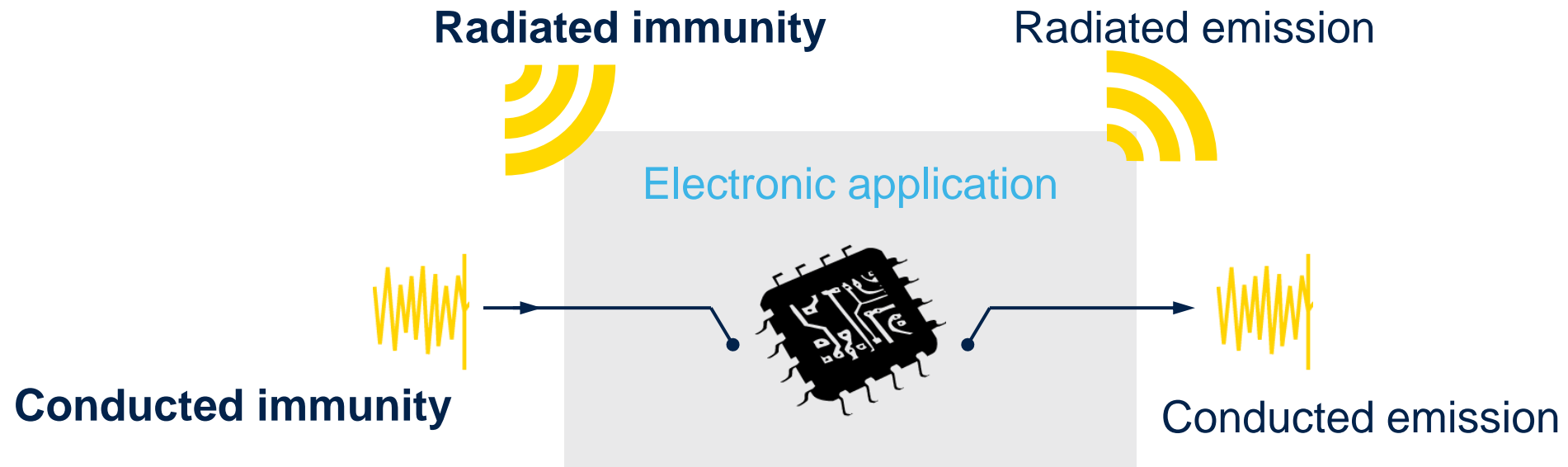
Introduction



Defining EMC immunity

What is EMC immunity ?

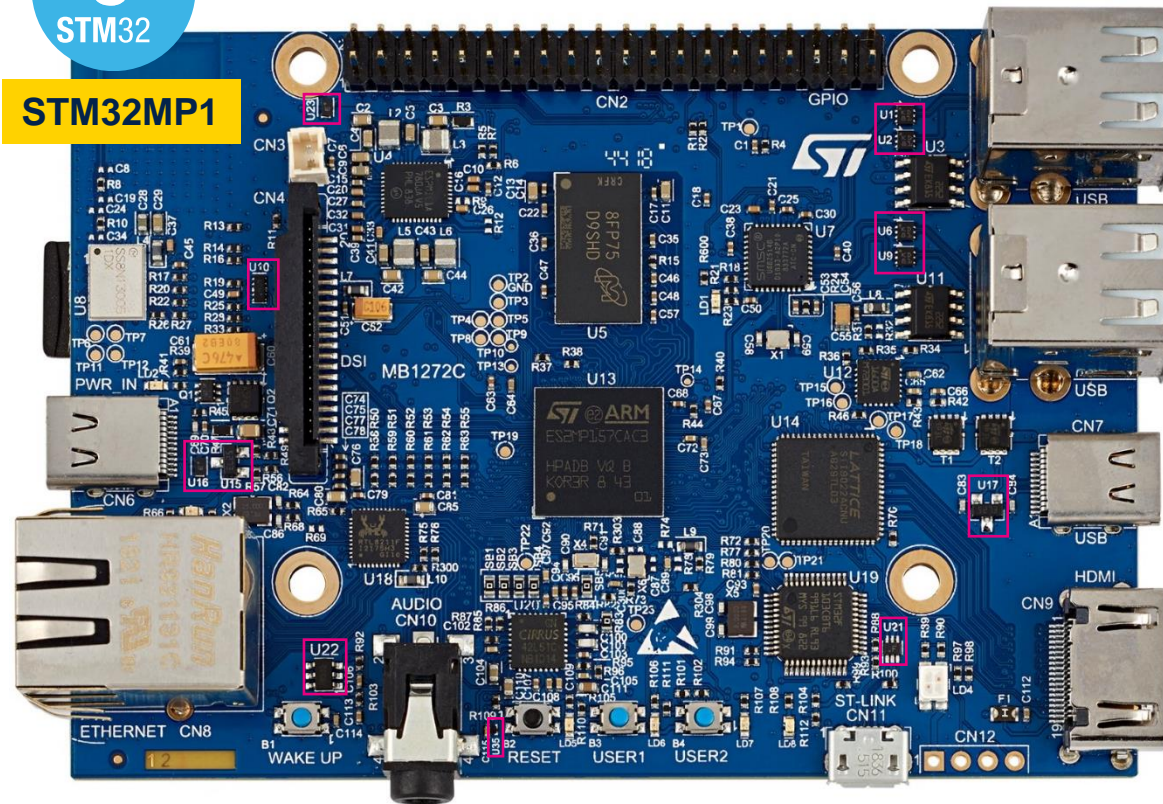
EMC Immunity is the ability of an equipment to properly operate in its electromagnetic environment by limiting the interference of electromagnetic energy that may cause physical damage.



EMC immunity example discovery kit: STM32MP157A-DK1



STM32MP1



MORPHO CONNECTOR
ESDA7P120-1U1M



5V Vin



MICRO SD CARD
HSP051-4M10 (x2)



SDMMC dataline



USB Type-C Power Delivery
ESDA7P120-1U1M, ESDA25L



VBUS



CC1, CC2



ETHERNET
HSP053-4M5



USB HOST x2 (Dual USB Type-A)
ESDA7P120-1U1M (x2), ECMF02-2AMX6 (x2)



VBUS



DP, DM



USB HOST x2 (Dual USB Type-A)
ESDA7P120-1U1M (x2), ECMF02-2AMX6 (x2)



VBUS



DP, DM



USB Type-C DRP (Source Only)
ESDA7P120-1U1M, ESDA25L, ECMF02-2AMX6



VBUS



CC1, CC2



DP, DM



HDMI
ECMF04-4HSWM10 (x2), ESDALC6V1-5M6



TMDs datalines



CEC, I2C, HPD



AUDIO
ESDA6V1BC6: 4-line ESD protection

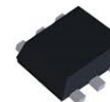


OUTA, OUTB, MIC IN

USER BUTTONS
ESDALC6V1-U2



ST-LINK USB CONNECTOR
USBLC6-2P6



DP, DM, VBUS



life.augmented



STM32 MPU by



Agenda

- 1 ESD Protection at System Level
- 2 How to select an ESD protection device?
- 3 ESD Layout Guidelines
- 4 Application Examples

ESD protection at system level



How is ESD generated ?

Triboelectric Charge

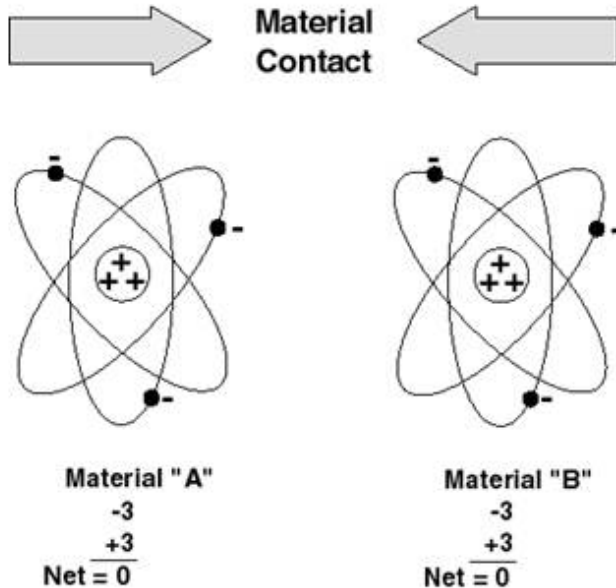


Figure 1 The Triboelectric Charge. Materials Make Intimate Contact

Triboelectric Charge

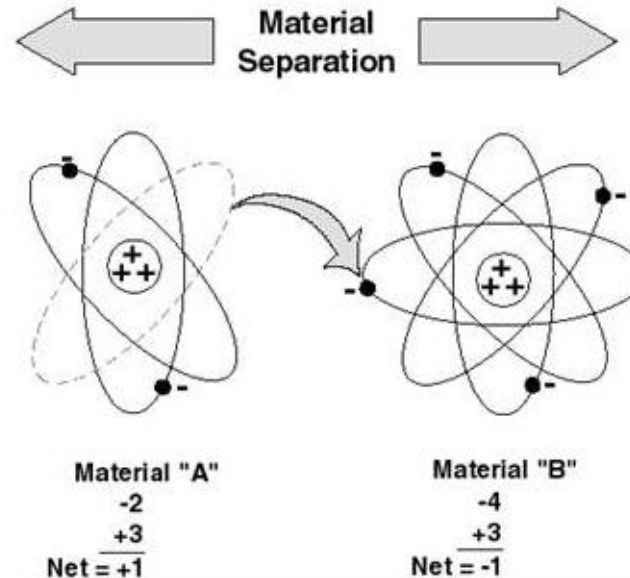


Figure 2 The Triboelectric Charge - Separation

Table 1
Examples of Static Generation - Typical Voltage Levels

Means of Generation	10-25% RH	65-90% RH
Walking Across Carpet	35,000V	1,500V
Walking Across Vinyl Tile	12,000V	250V
Worker at a Bench	6,000V	100V
Poly Bag Picked up from Bench	20,000V	1,200V
Chair with Urethane Foam	18,000V	1,500V

ESD damages to ICs

White Paper on Electrical Overstress - EOS Industry Council on ESD Target Levels

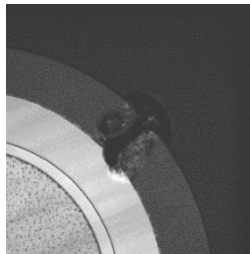
In preparation for this white paper, the Industry Council conducted a worldwide survey of the electronics industry concerning EOS. Results confirmed the long held view that EOS is consistently one of the “high bars” on product failure Pareto charts. Looking at the EOS survey, respondents reported greater than 20% of total failures being EOS-related or **30% of total electrical failures being EOS-related**, making EOS the largest bar on the Pareto chart of that responder’s known causes of returns.

Source: <https://pdfs.semanticscholar.org/235b/0bfd01dd5f0c6c2c99df3b93bc27f56a9cfd.pdf>

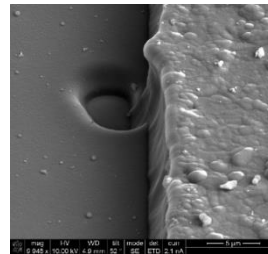


“30% of total electrical failure is EOS -related”

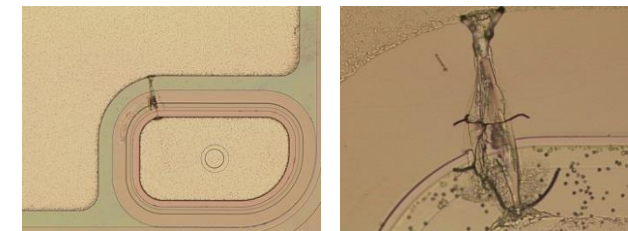
Silicon melting



Hole in the oxide

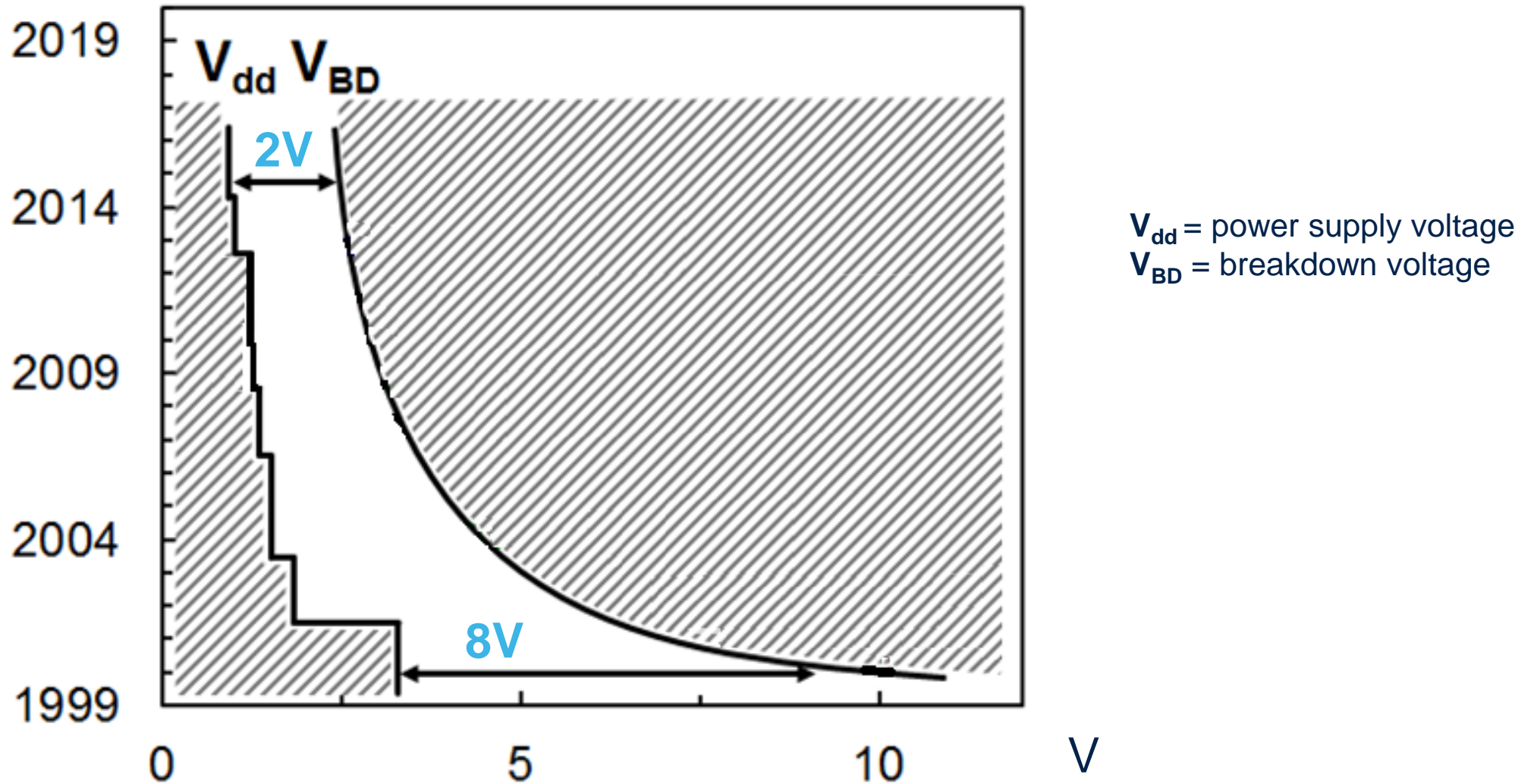


Melting Flash

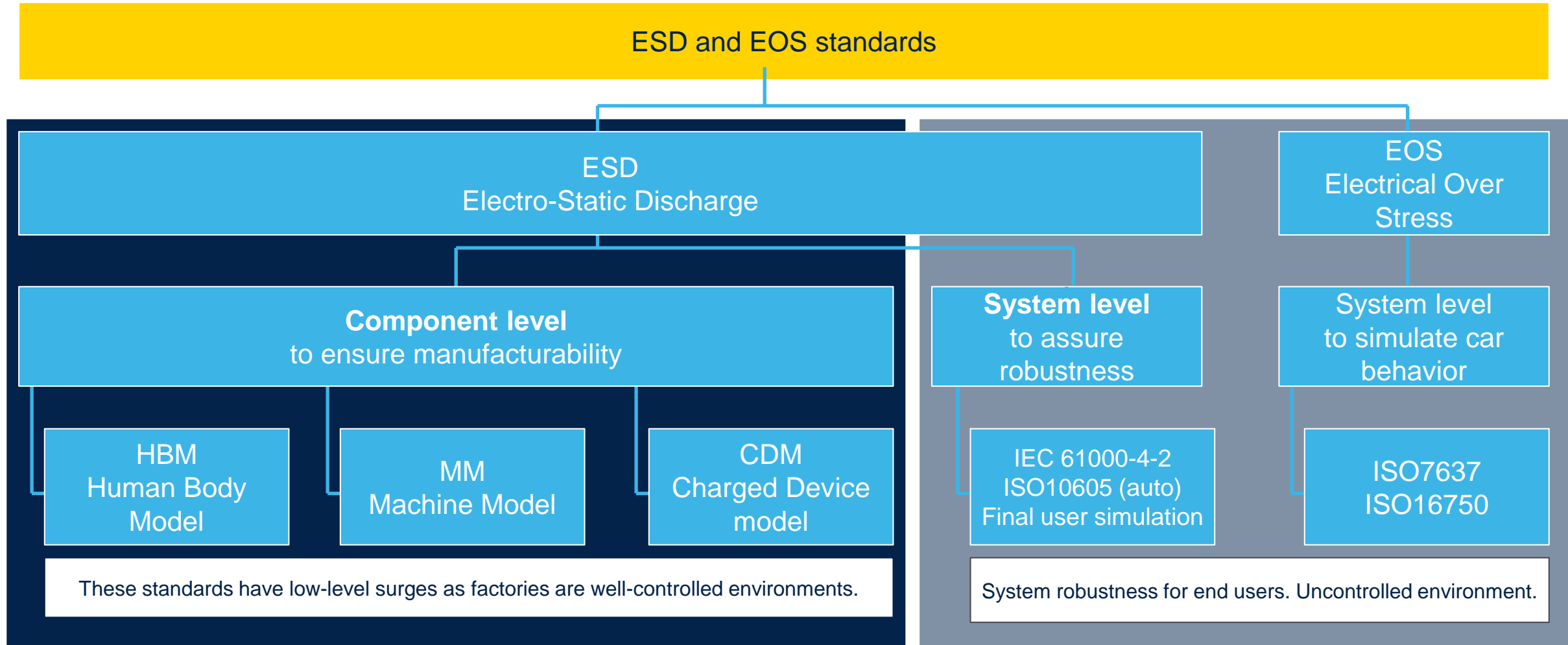


Source: STMicroelectronics

ESD sensitivity is increasing



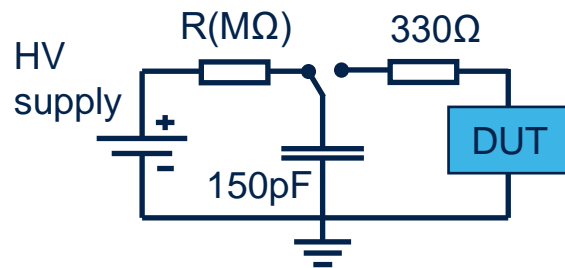
ESD and EOS standards



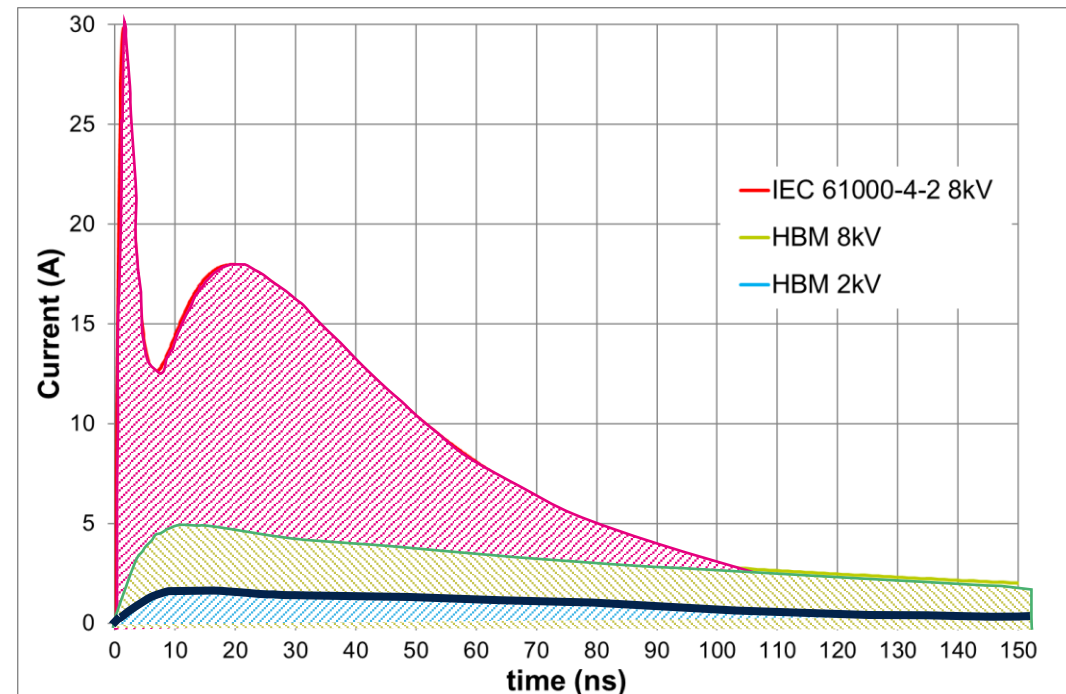
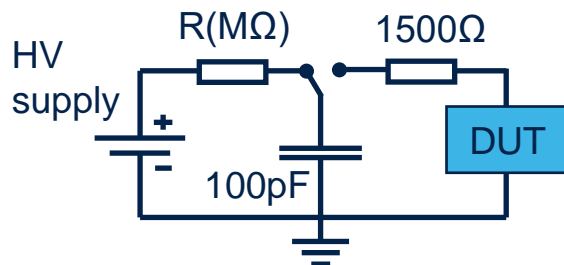
HBM and IEC standards

Difference in standards : IEC 61000-4-2 carries more energy than HBM

IEC 61000-4-2 for system
($\pm 8\text{kV}$ for level 4)



Human Body Model for IC
($\pm 2\text{kV}$ for most of IC)



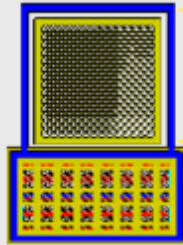
Energy for 8kV IEC 61000-4-2

Energy for 8kV HBM

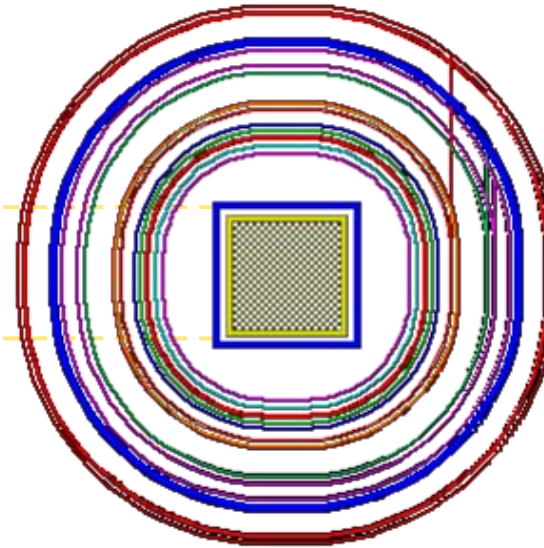
Energy for 2kV HBM

Component VS system level silicon die area comparison

Silicon die area for
component level ESD
(2 kV HBM)



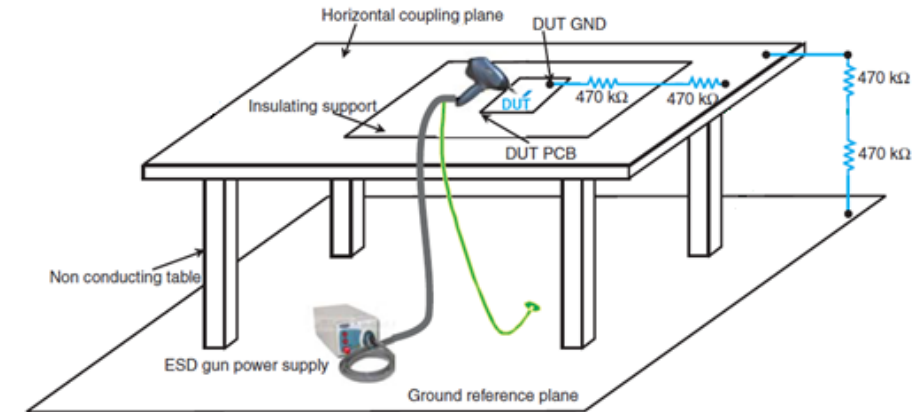
Silicon die area for
system level ESD
(8 kV IEC contact)



System-level ESD protection standard

IEC 61000-4-2 test bench

	Contact discharge	Air discharge	
Stress Level	Test Voltage (kV)	Test Voltage (kV)	Number of discharges
1	2	4	At least 10 single discharges at 1 Hz in the most sensitive polarity
2	4	6	
3	6	8	
4	8	15	



System state as a result of system-level ESD stress

A	Normal performance
B	Temporary loss of function or degradation of performance which cease after the disturbance ceases. The DUT recover its normal performance , without operator intervention
C	Temporary loss of function or degradation of performance , the correction of which requires operator intervention
D	loss of function or degradation of performance, no recovery possible

Self-restored

Require a system reset

ESD in automotive: ISO10605

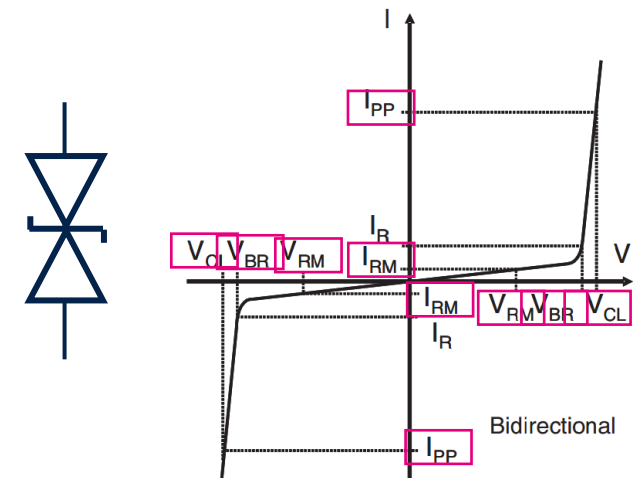
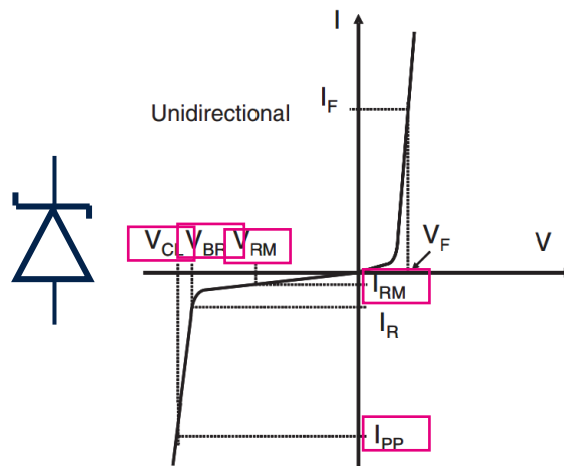
Configuration	Mode	Component accessible from:	Test (A= Air C= contact)	Capacitance	Resistance	Max test voltage	Operating conditions	Min number of discharges	Min. time interval	Max suggested severity levels (ISO10605 Annex C)
Component	Direct	Inside	A & C	330 pF	330 ohm	-	Powered	3	1s	15 kV C 25kV A
Component	Direct	Outside	A & C	150 pF	330 ohm	-	Powered	3	1s	15 kV C 25kV A
Component	Indirect	Inside	C	330 pF	330 ohm	-	Powered	50	50ms	20kV C
Component	Indirect	Outside	C	150 pF	330 ohm	-	Powered	50	1s	20kV C
Component packaging and handling	Direct	NA	A & C	150 pF	330 or 2000 ohm	-	Unpowered	3	1s	
Vehicle test	Direct	Inside	A & C	330 pF	330 or 2000 ohm	15 kV	Engine drive or idle	3	1s	8kV C 15kV A
Vehicle test	Direct	Outside	A & C	150 pF	330 or 2000 ohm	25 kV	Engine drive or idle	3	1s	8kV C 25kV A

How to select an ESD protection device



Key parameters

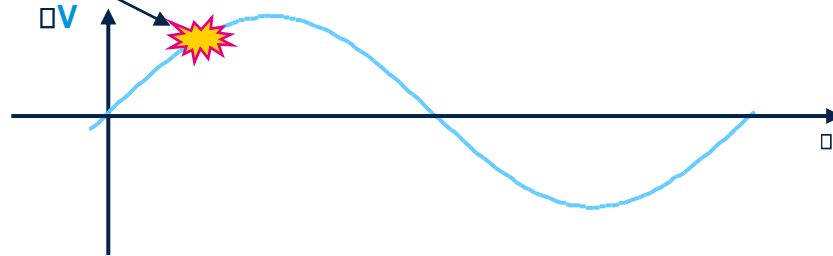
Parameters	Description
V_{RM}	Stand-off voltage (normal condition voltage)
I_{RM}	Leakage current
V_{BR}	Breakdown voltage (voltage when the ESD protection starts working)
V_{CL}	Clamping voltage (maximum voltage accross the ESD protection)
I_{PP}	Peak Pulse Current (maximum current in the ESD protection)
C	Line capacitance (impacts signal integrity)



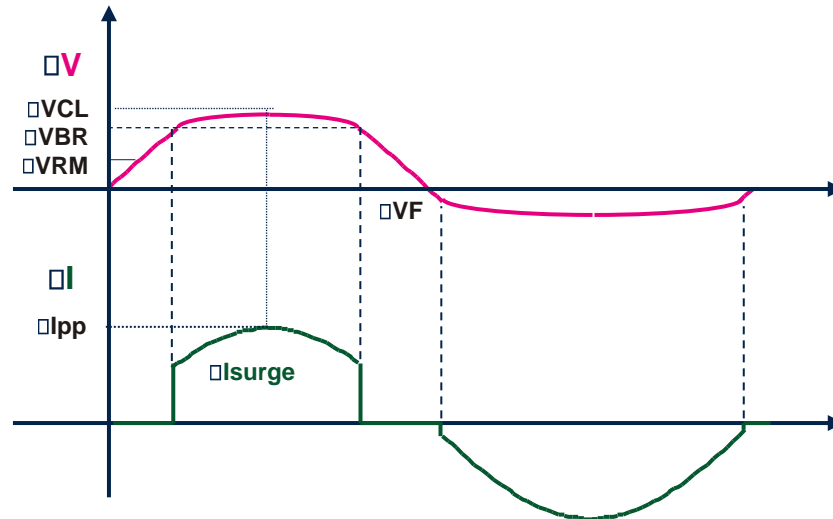
Protection selection key parameter : voltage

No TVS
protection

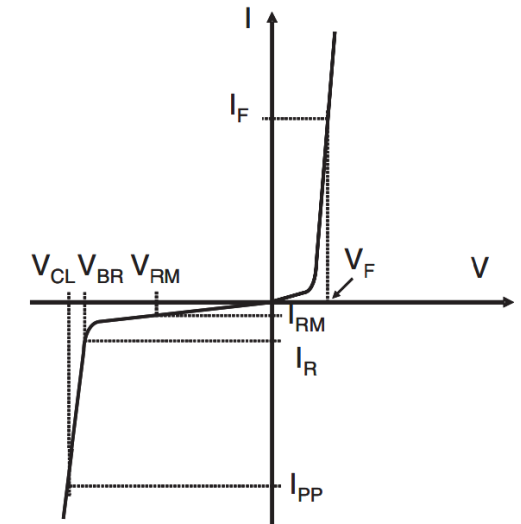
Failure



With TVS
protection



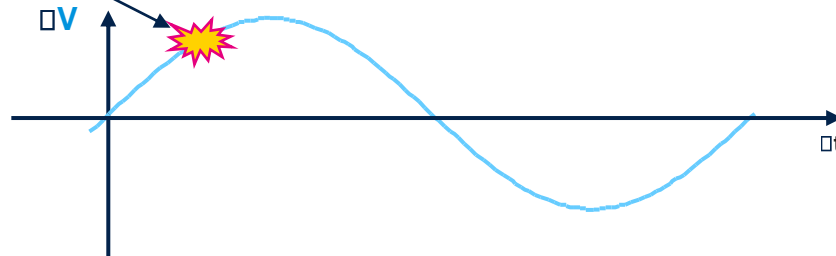
Uni-directional



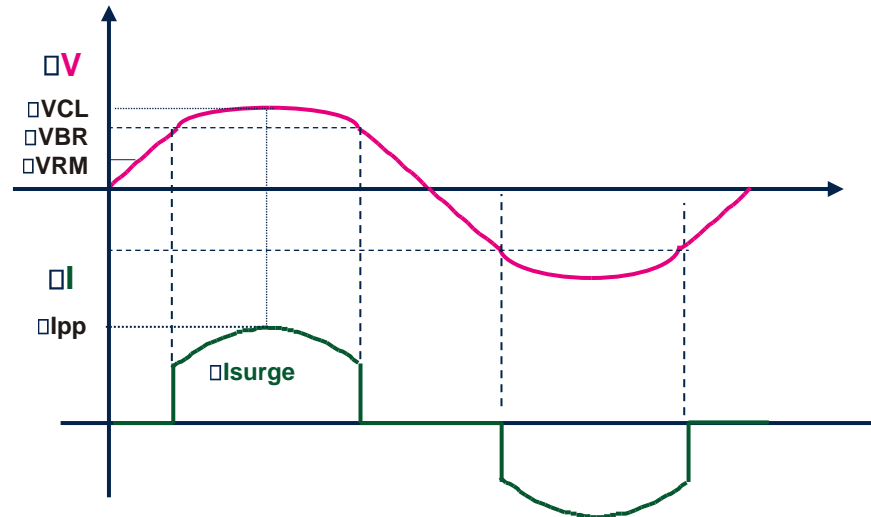
Key parameters voltage polarity

No TVS
protection

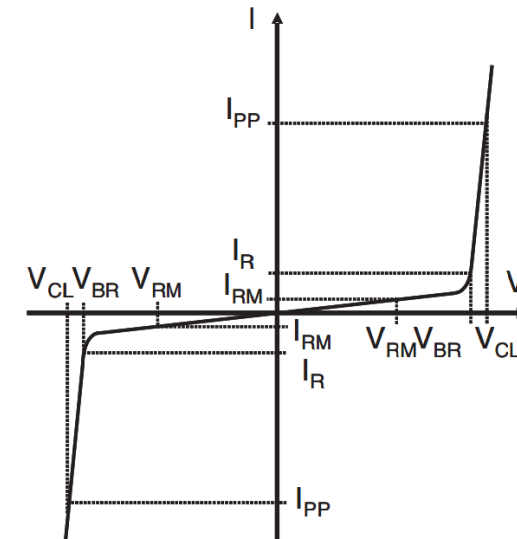
Failure



With TVS
protection



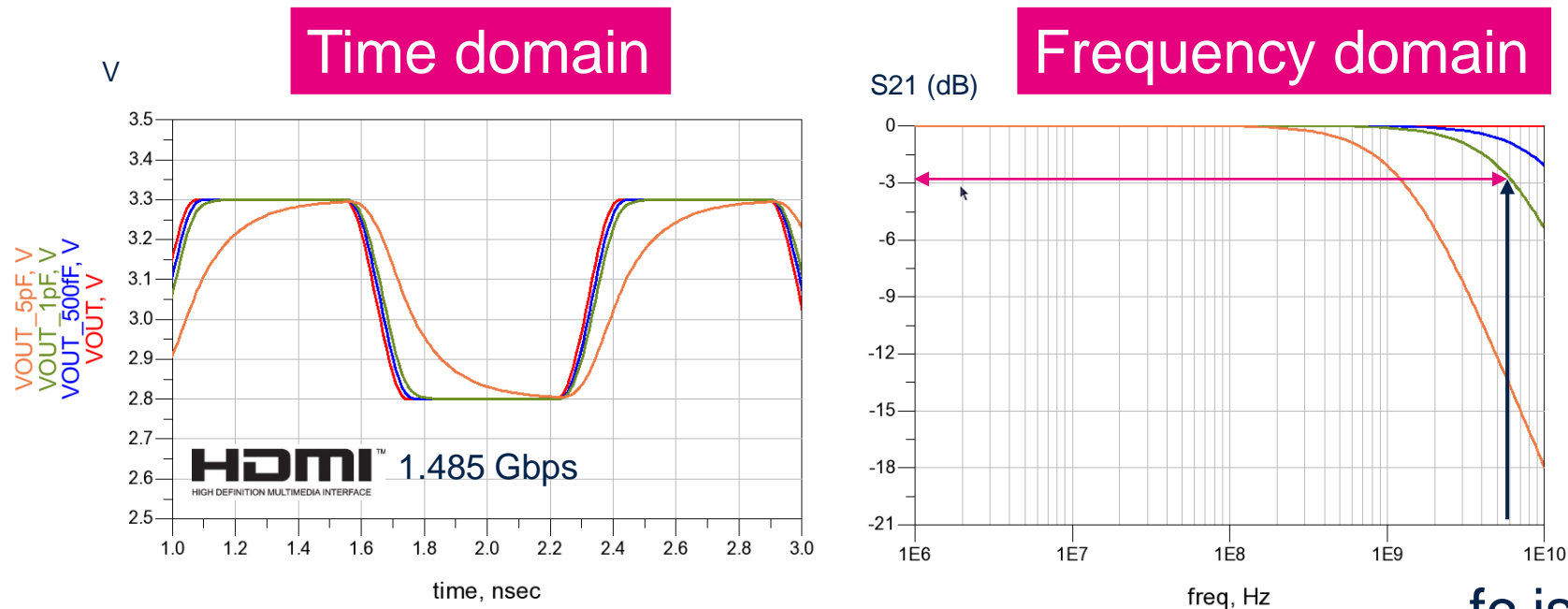
Bi-directional



- Mandatory for audio and RF signals

Key parameters capacitance value

- Example of the impact of parasitic capacitance on high-speed signal simulated with discrete capacitance

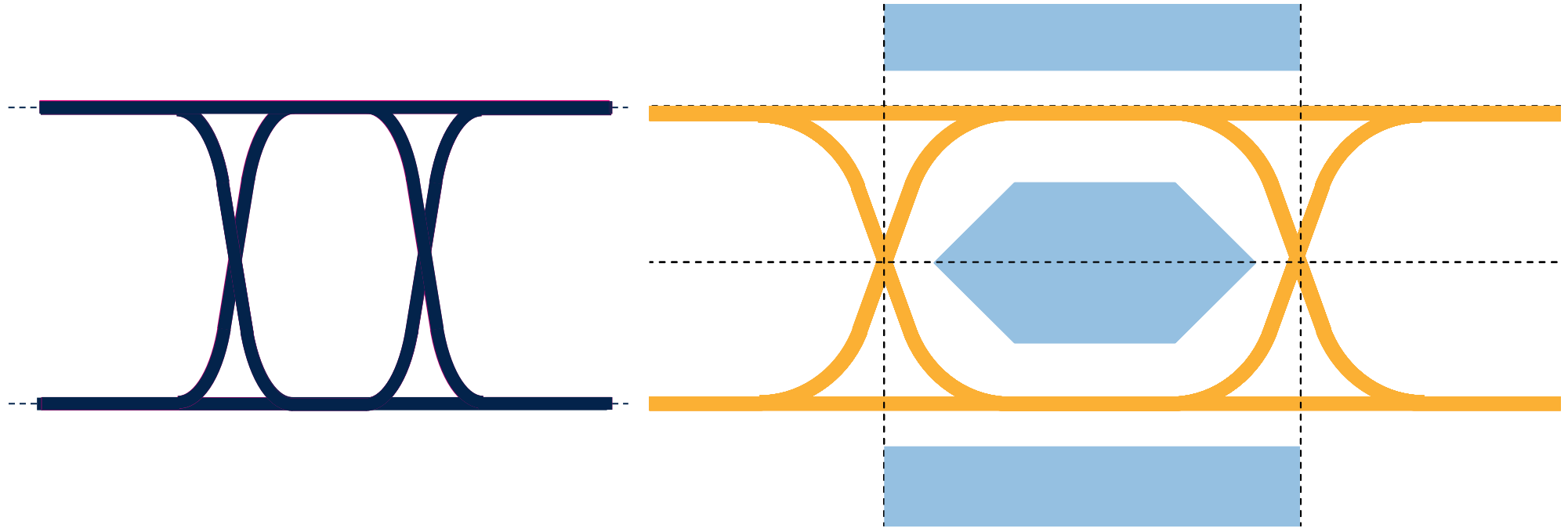
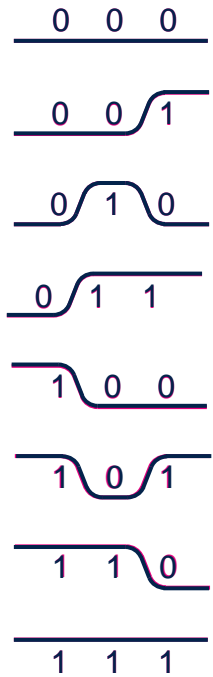


$$f_c = \frac{1}{\pi t_r}$$

f_c is high enough
to comply with
HDMI 1.485 Gbps

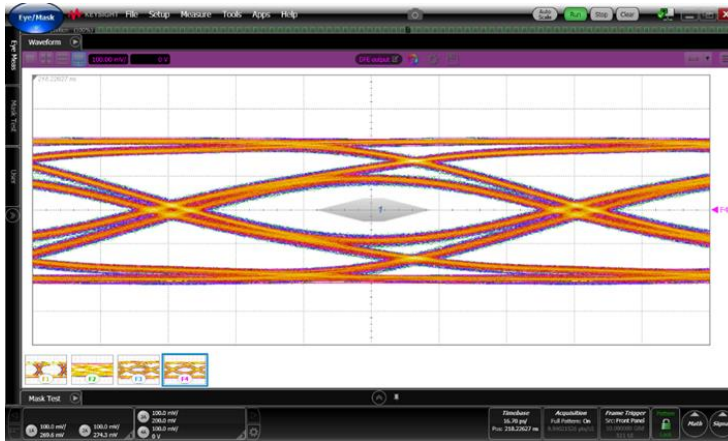
Eye diagram

what is an eye diagram?

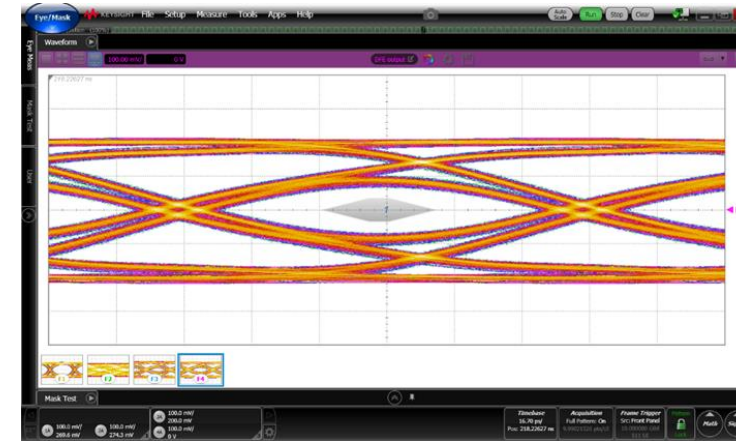


Impact on data-lines eye diagram integrity

- USB 3.1 Gen2 mask at 10.0 Gbps per channel
(Type-C connector, reference cable, EQ with DC=6dB and DFE)



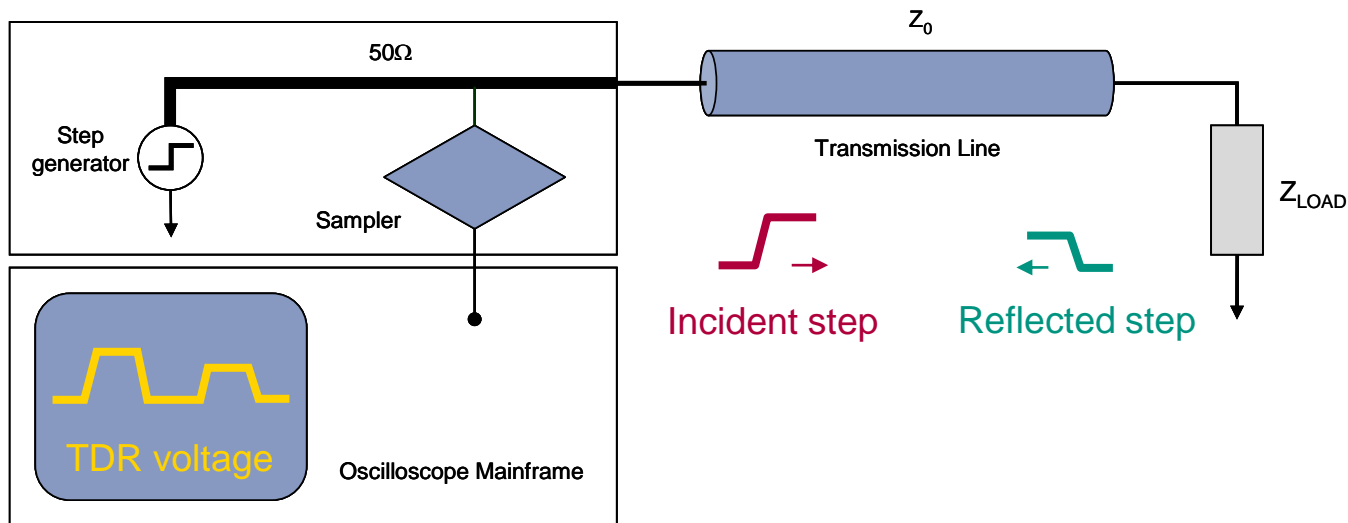
Line without HSP053-4M5



Line with HSP053-4M5

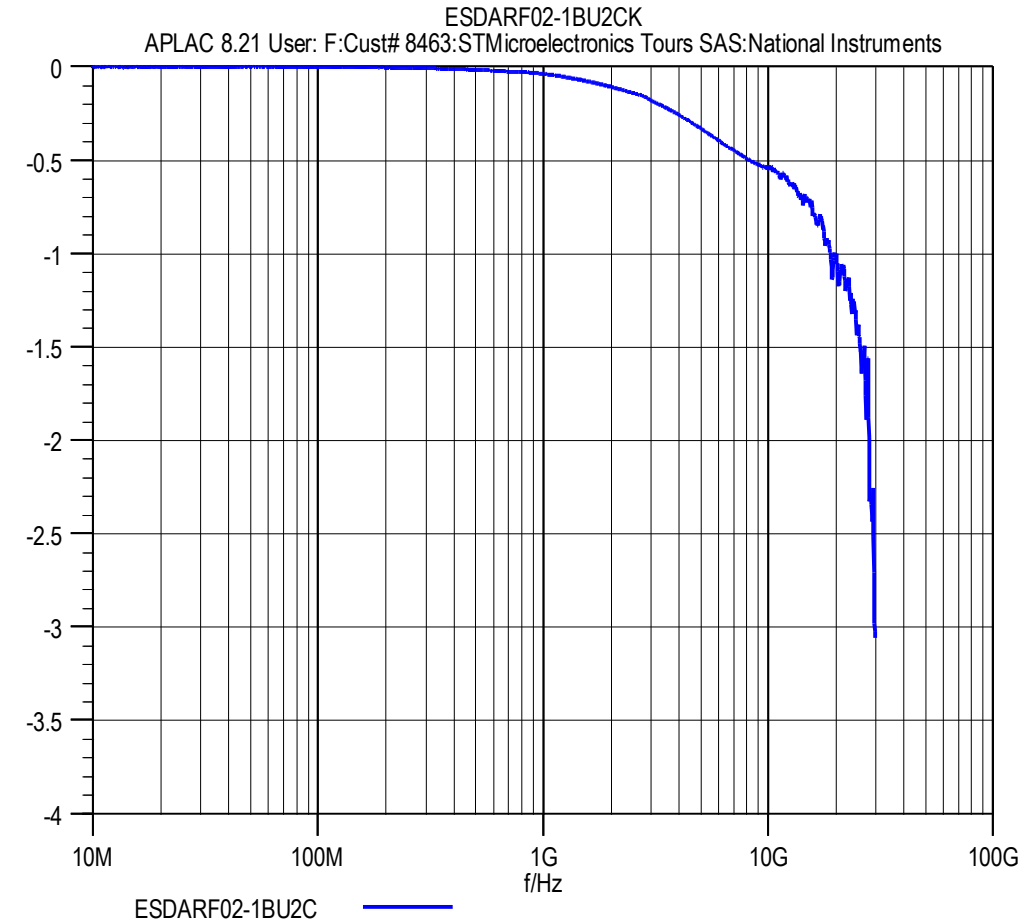
Impact on data-lines time domain reflectometer impedance

TDR with 200ps pulse rise time impedance of
100Ω line **without** / **with** HSP053-4M5



Impact on RF signal S21 attenuation

- ESDARF02-1BU2CK S21
 - 30 GHz at -3 dB
 - 8 GHz at -0.5 dB
- Negligible impact major frequencies for teleco
 - FM radio : 87.5 MHz - 108.0 MHz
 - Numerical TV : 400 MHz – 900 MHz
 - Cellular phones : 700 MHz ... 4.7 GHz
 - GNSS : 1.6 GHz
 - Bluetooth : 2.4 GHz
 - Sub-GHz industrial : 400 MHz ... 1.1GHz
 - WiFi : 2.4 / 5.0 GHz

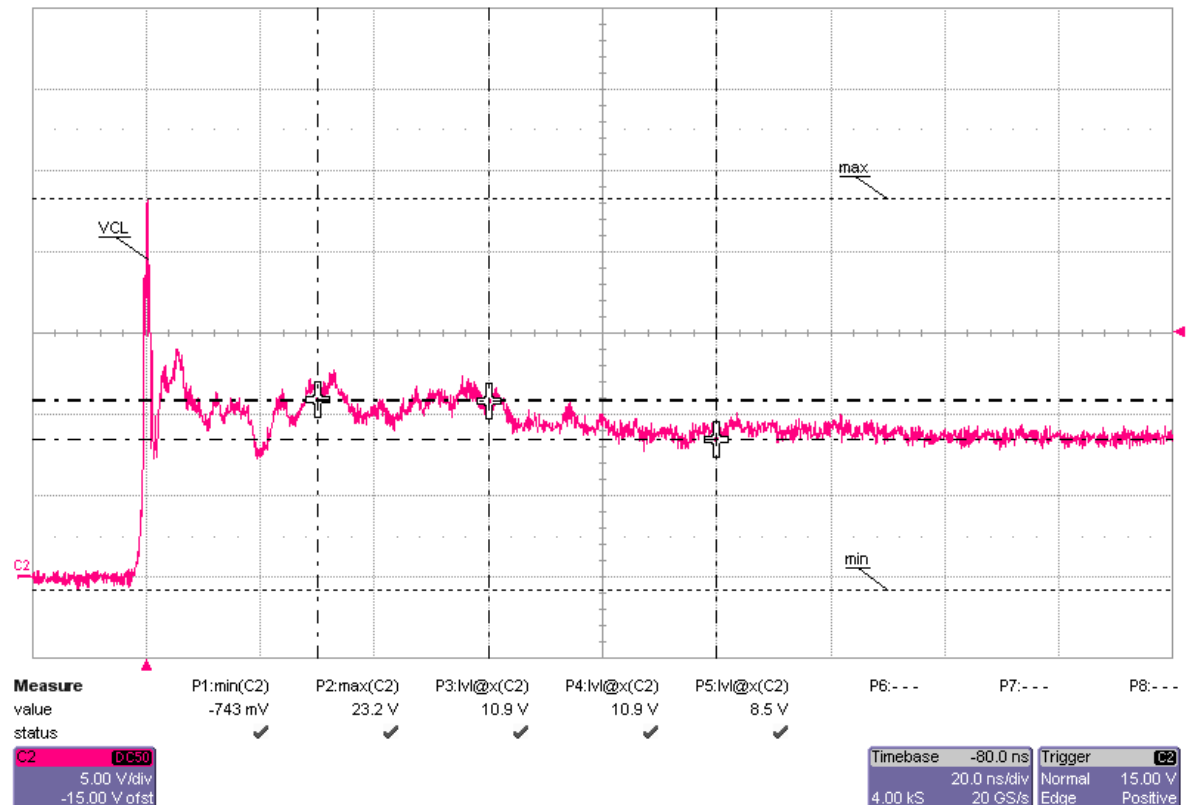


ESD protection

IEC 61000-4-2 +/-8kV ESD response

- IEC 61000-4-2 response of ESD051-1BF4 :
 - First peak : 23V (low energy, CDM like)
 - 30ns clamping : 11V (clamping voltage)

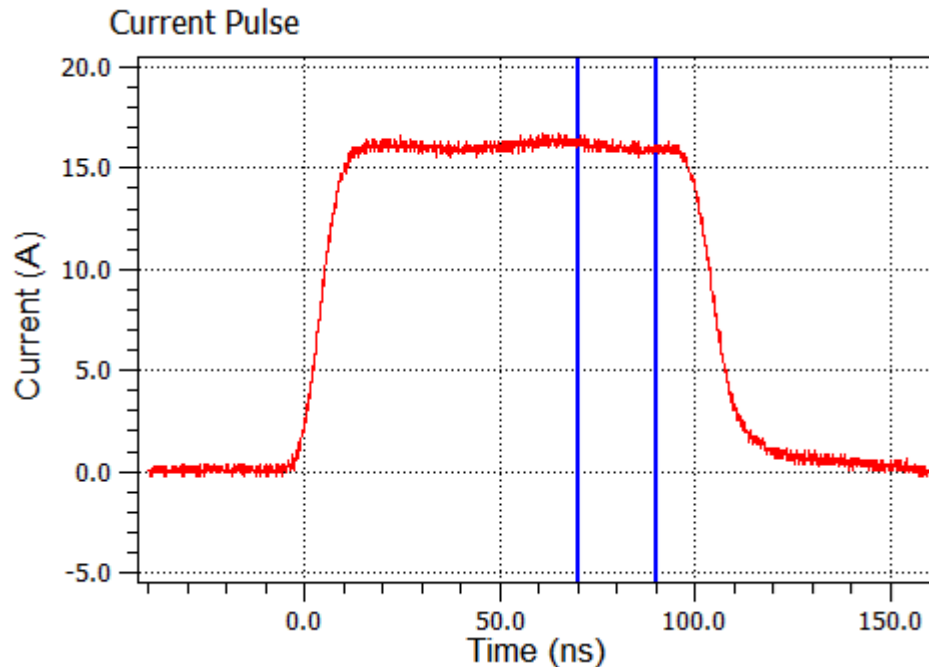
ESD051-1BF4 +8kV IEC 61000-4-2 response



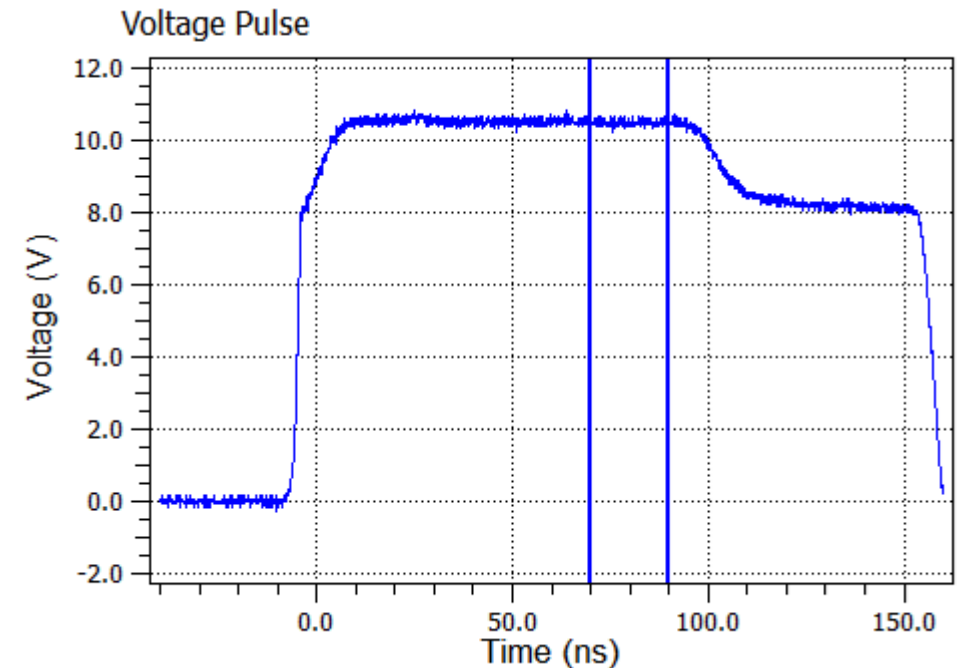
ESD protection Transmission Line Pulse

- IEC 61000-4-2 8 kV 30 ns clamping voltage \leftrightarrow TLP* 16 A 100 ns 70 - 90% voltage

Injected current :
16A – 100ns square current



Measured voltage on 70% – 90% windows
on ESD051-1BF4 : 10.5V

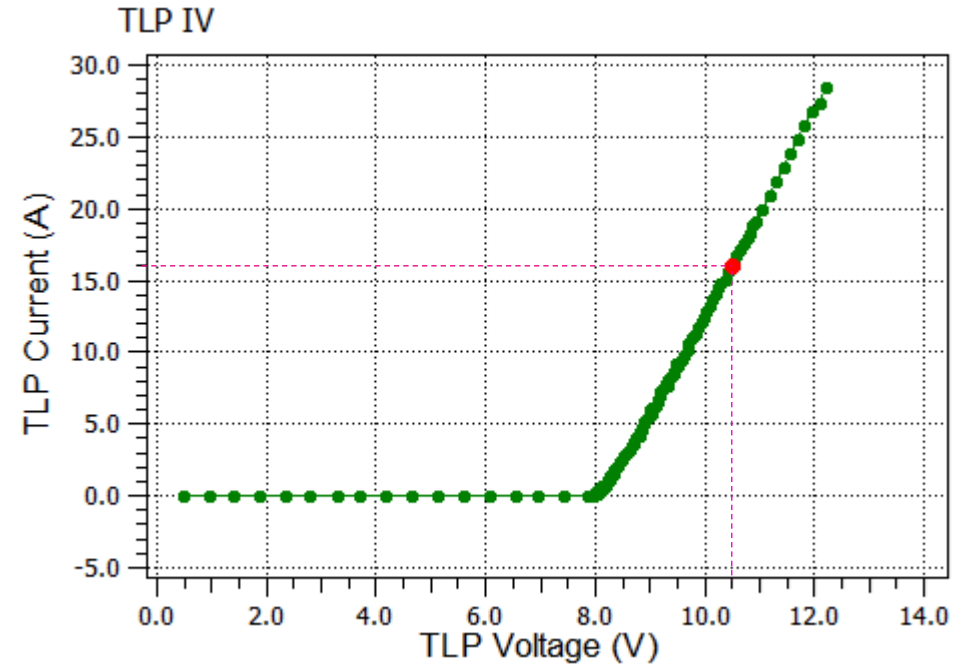


ESD protection

Transmission Line Pulse I/V curve

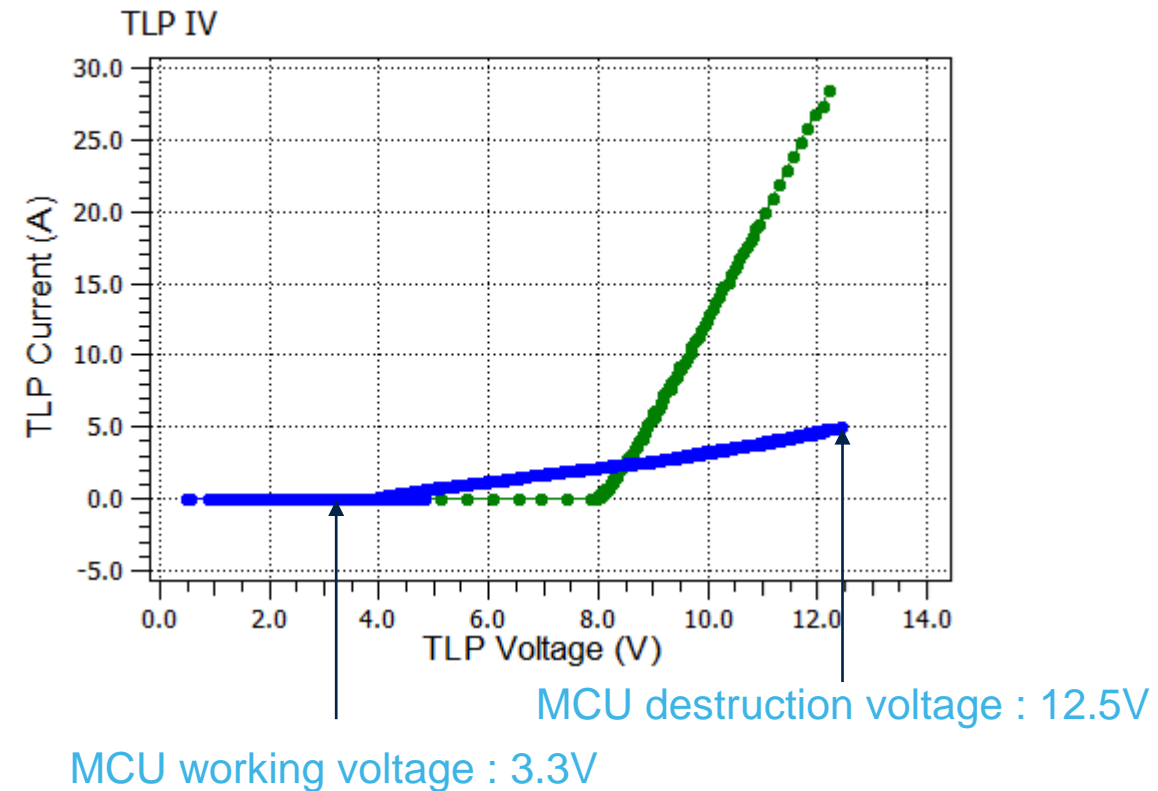
- I/V TLP* curve is done with several pulses

ESD051-1BF4 TLP* I/V curve



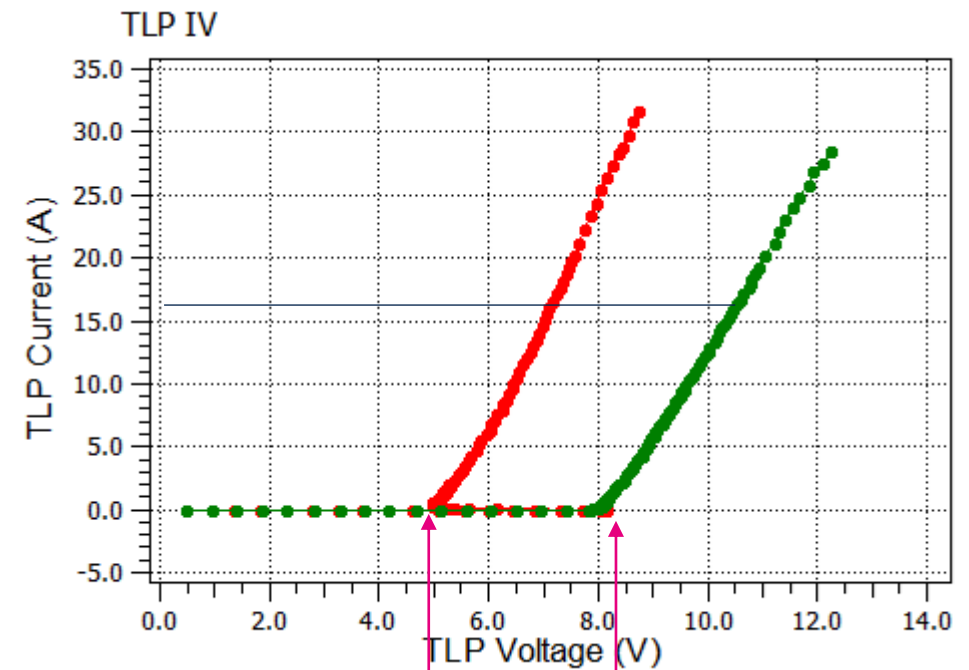
System-efficient ESD design methodology

- TLP input current shared between high performance MCU FT input and ESDA5-1BF4
- High performance MCU + ESDA5-1BF4 robustness reach more than 8kV IEC 61000-4-2
 - Even if, ESD5-1BF4 clamping voltage > High Performance MCU FT input AMR
- **ESD051-1BF4**
 - 11V clamping voltage at +8kV ESD 61000-4-2
- High Performance MCU FT input
 - 3.6 V max operating
 - 2 kV HBM ESD
 - 250 V CMD ESD
 - 5.5 V AMR



Snap-back protections system integration

- Snap-back protection (ESDZV5-1BF4) clamping voltage lower than standard protection (ESD051-1BF4) clamping voltage
- Protected line DC voltage MUST be lower than holding voltage
 - To avoid protection latch-up
i.e. continuous leakage current flowing into the protection

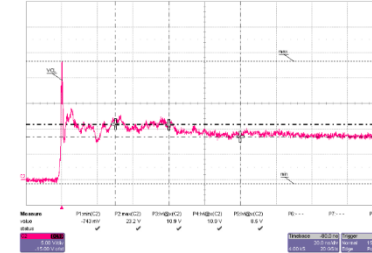
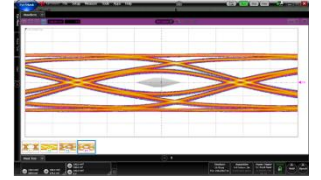
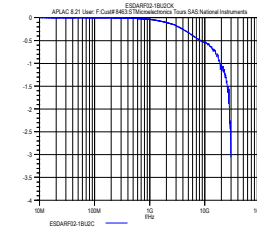


ESDZV5-1BF4
turn-on voltage

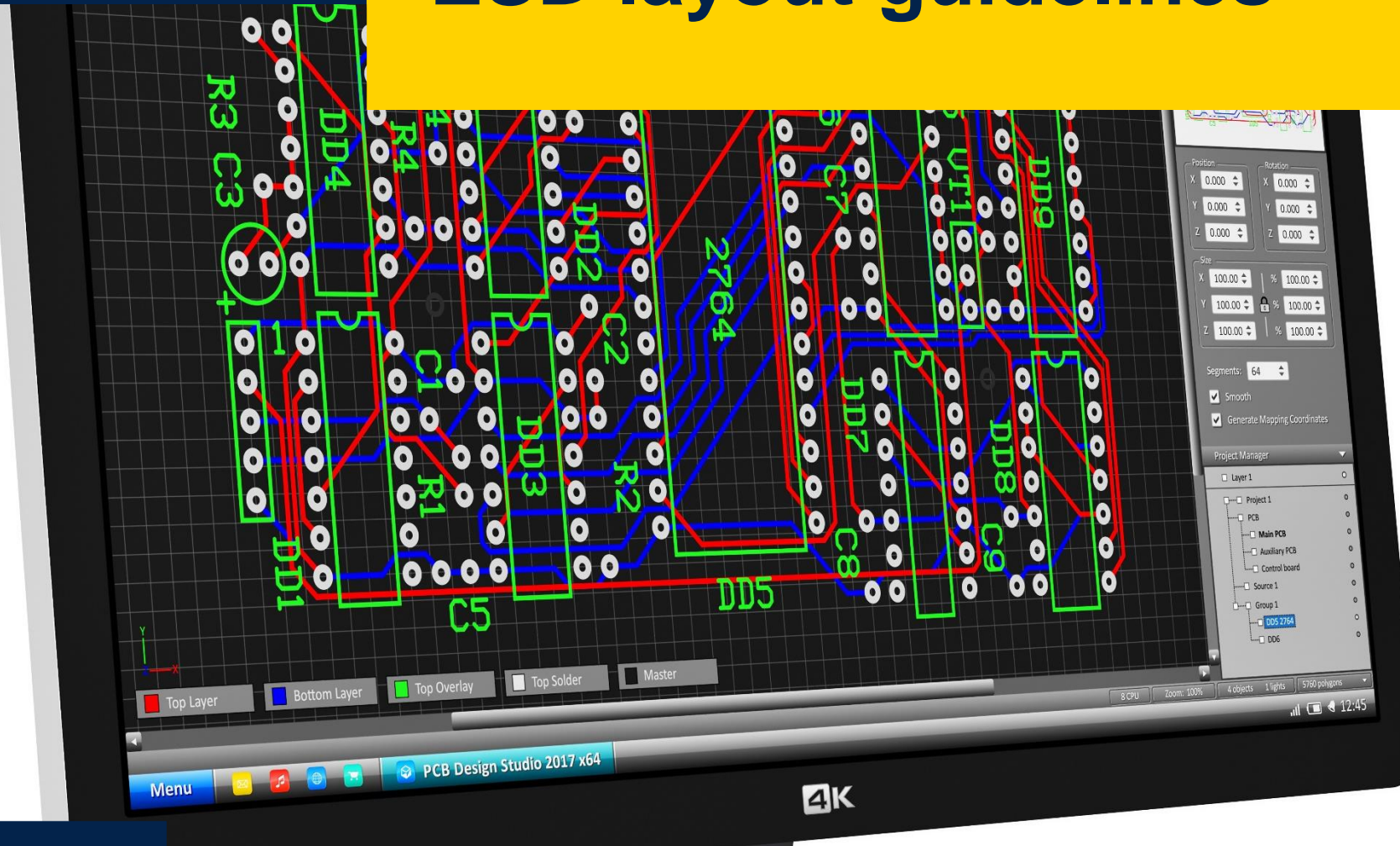
ESDZV5-1BF4
holding voltage

Recap basics of ESD protection

- Transparency :
 - Capacitance must be in-line with application bandwidth / data rate
- Efficiency :
 - VRM must be slightly higher than maximum line voltage
To obtain a low clamping voltage
- System integration of snap-back protection :
 - Holding voltage must be higher than DC voltage

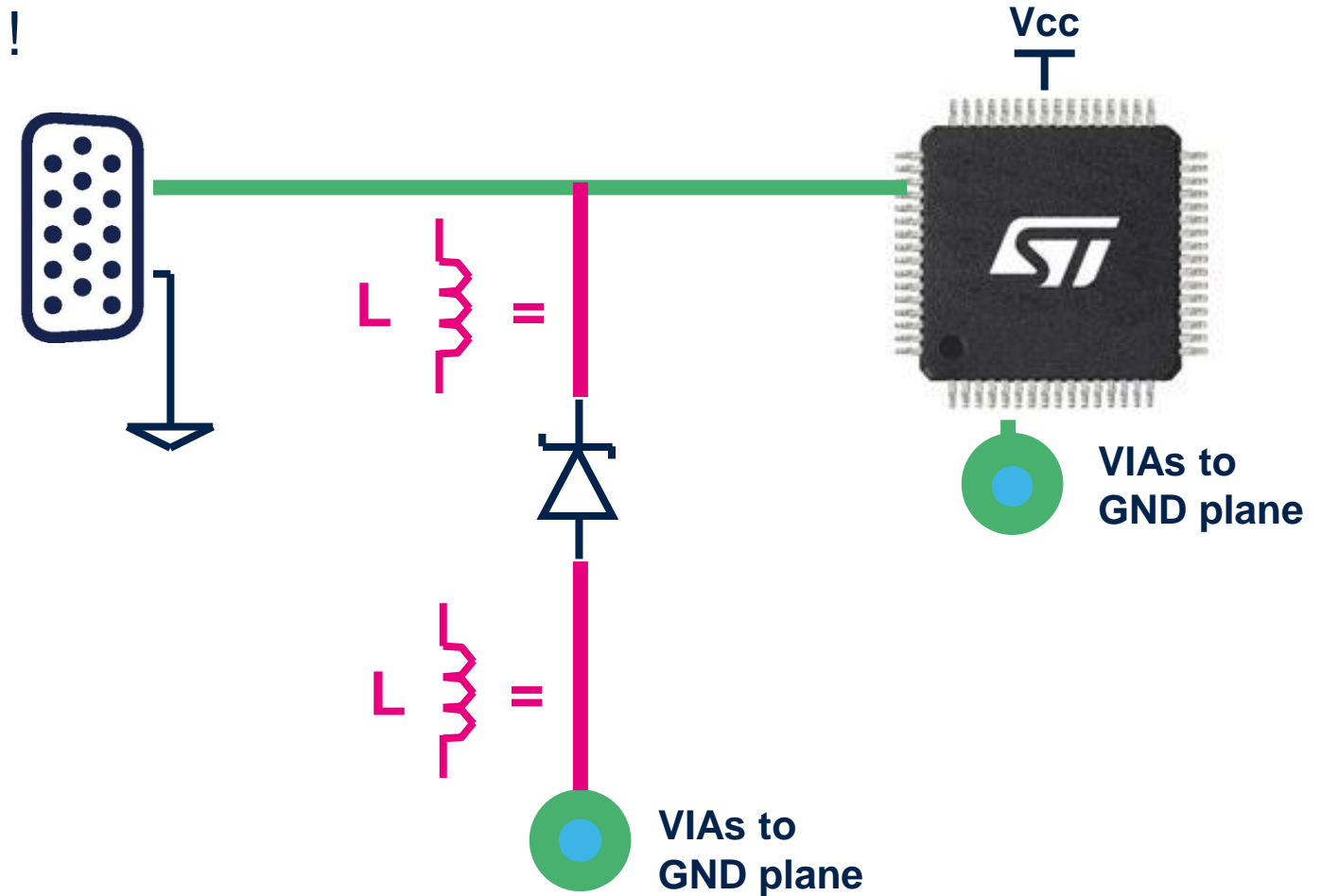


ESD layout guidelines



ESD robustness PCB layout impact

- PCB Tracks must be under control !
- For protection device length connection of ~1cm from side to side, 35 μ m copper, 0.5mm wide (microstrip)
- $2 \times L = 5 \text{ nH} !$



ESD robustness PCB layout impact

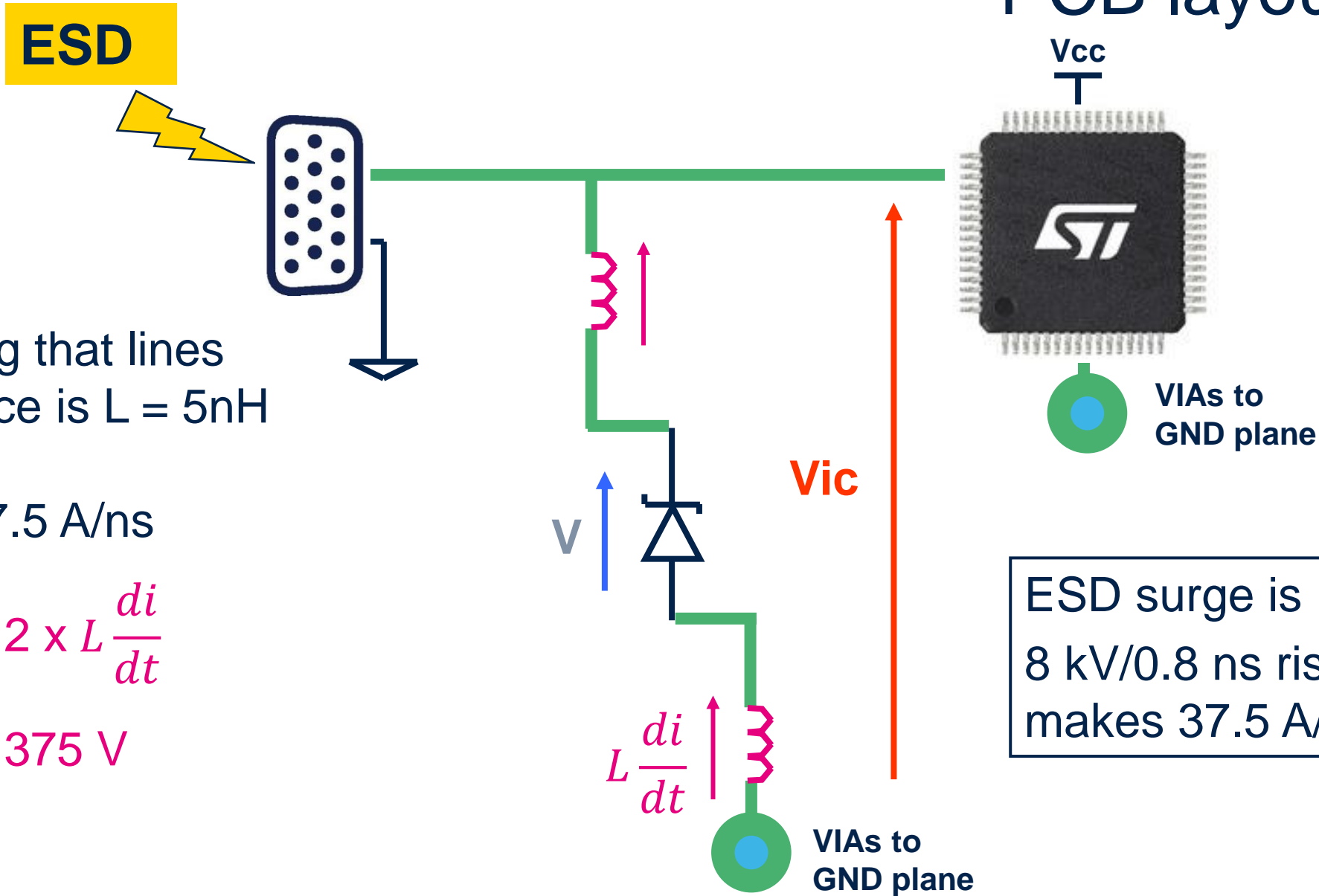
- $L \frac{di}{dt}$

Assuming that lines inductance is $L = 5\text{nH}$

$$di/dt = 37.5 \text{ A/ns}$$

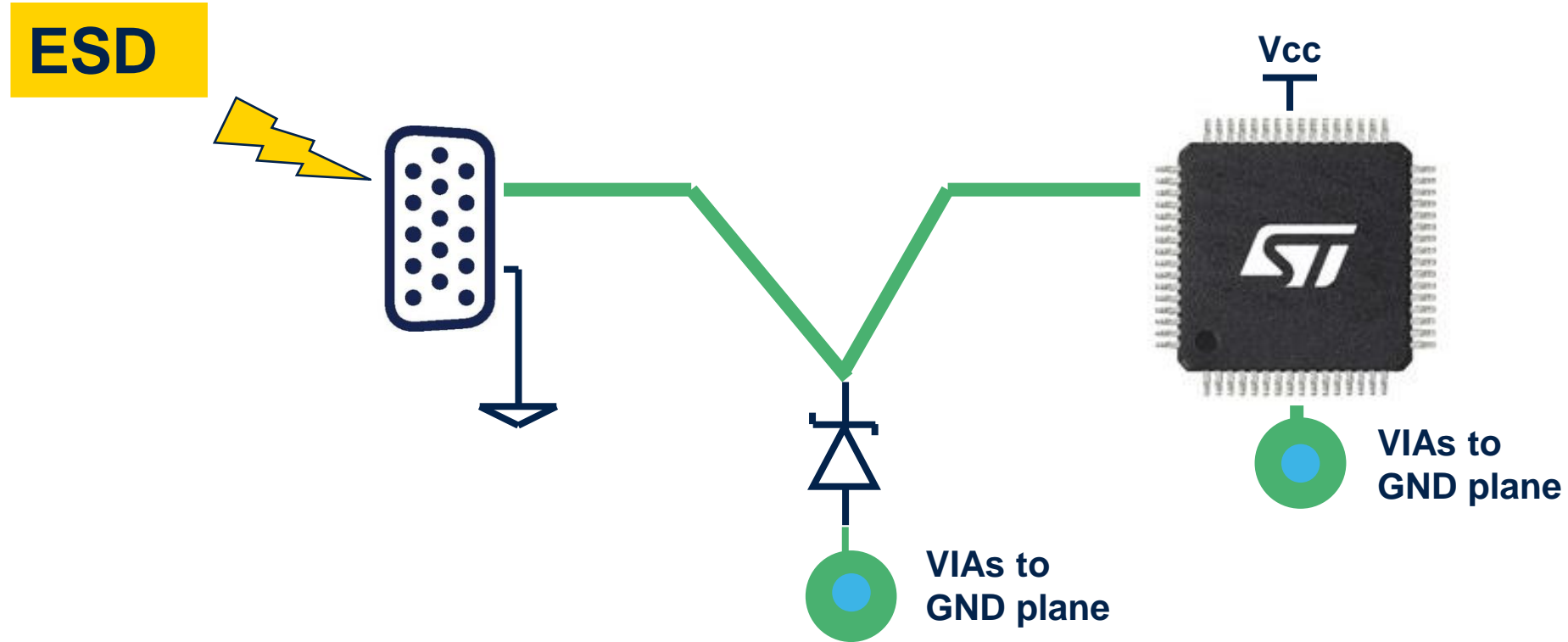
$$V_{ic} = V + 2 \times L \frac{di}{dt}$$

$$V_{ic} = V + 375 \text{ V}$$



ESD surge is
8 kV/0.8 ns rise time, this
makes 37.5 A/ns

ESD robustness PCB layout recommendation

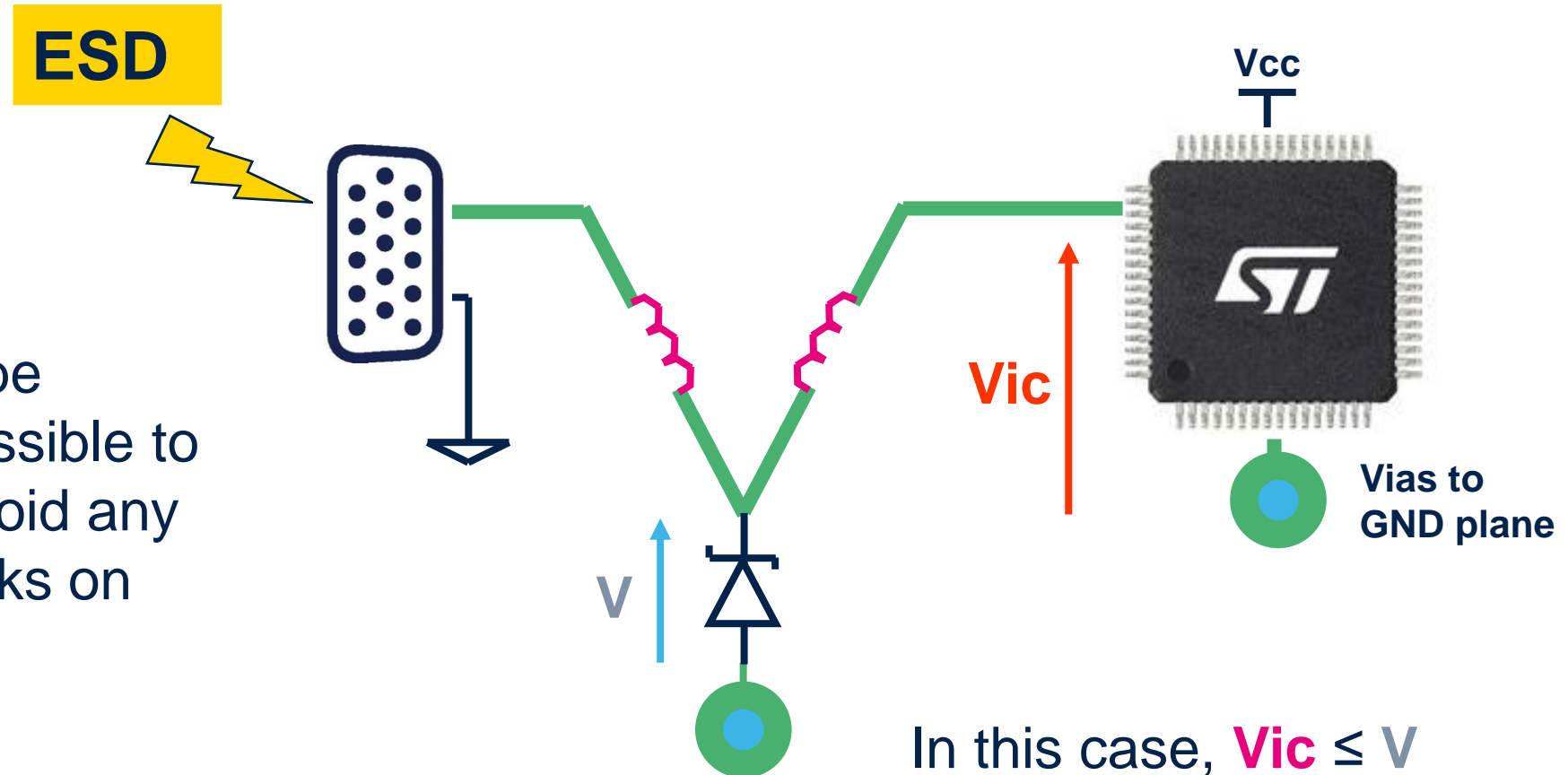


VIAs to GND plane as close as possible to the product GND

ESD robustness PCB layout recommendation

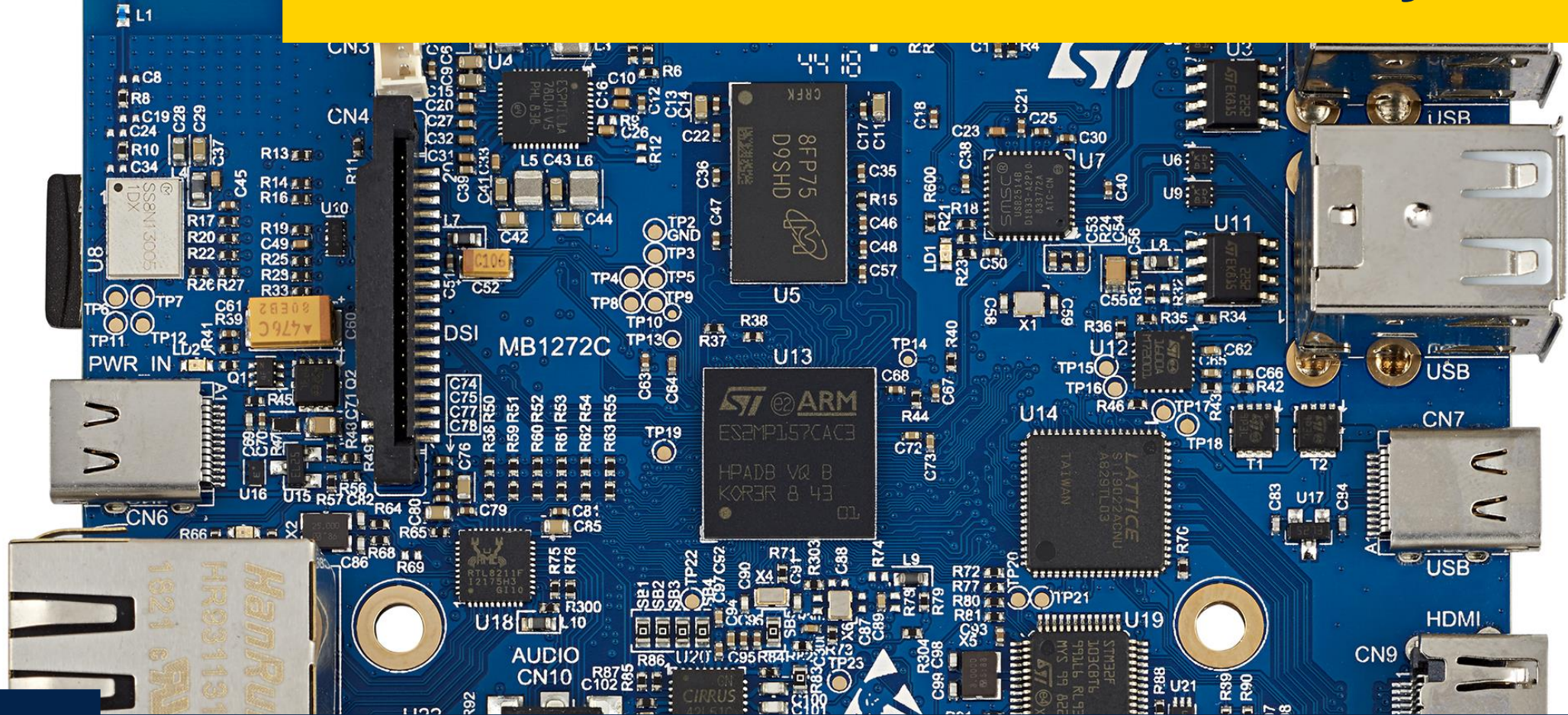
- PCB Layout recommendations in Application note [AN1751](#)

- ESD protection must be placed as close as possible to the ESD source, to avoid any coupling between tracks on the PCB.

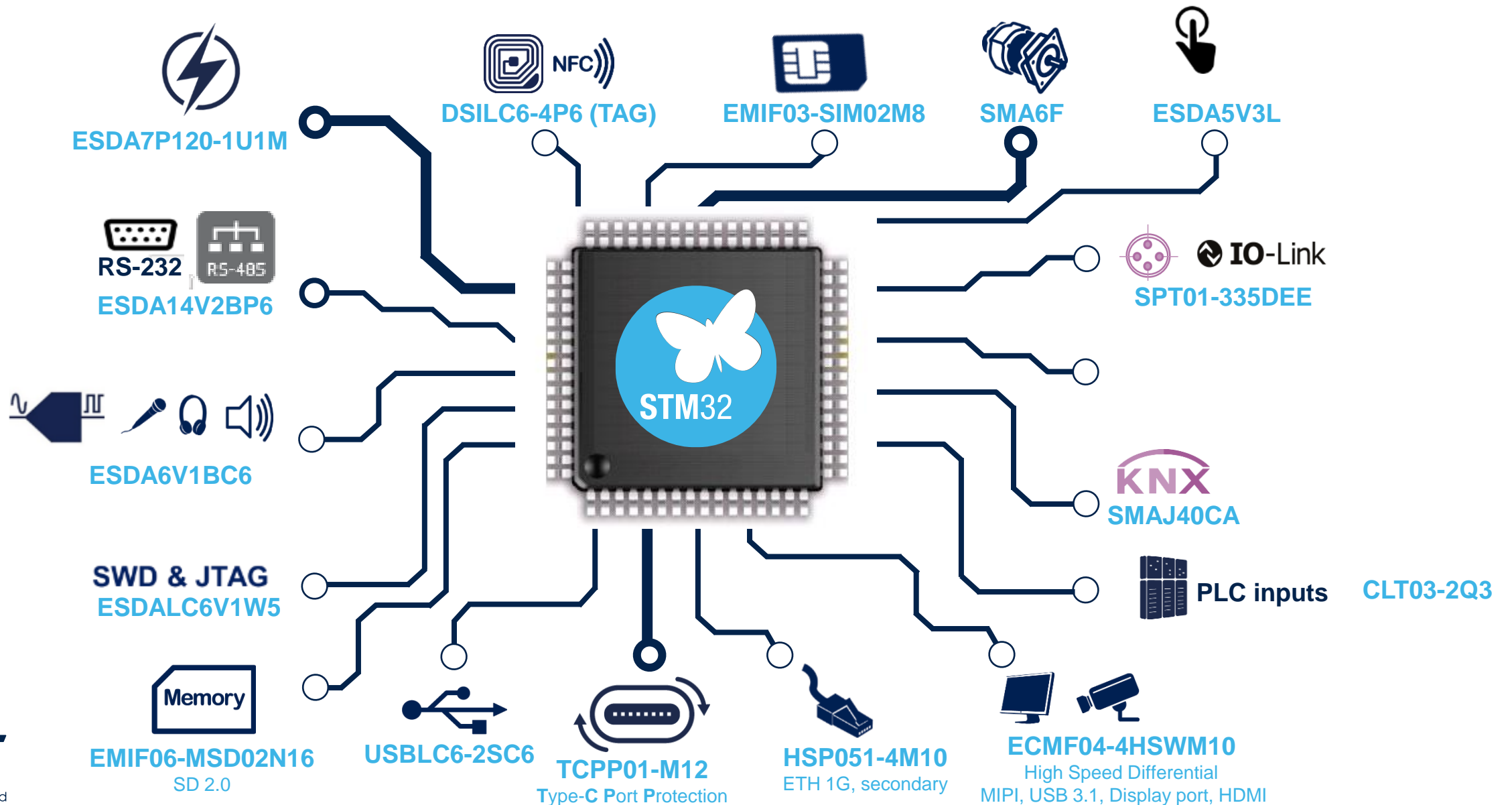


Application examples

Protection devices and PCB layouts



Protections and filters around MCUs

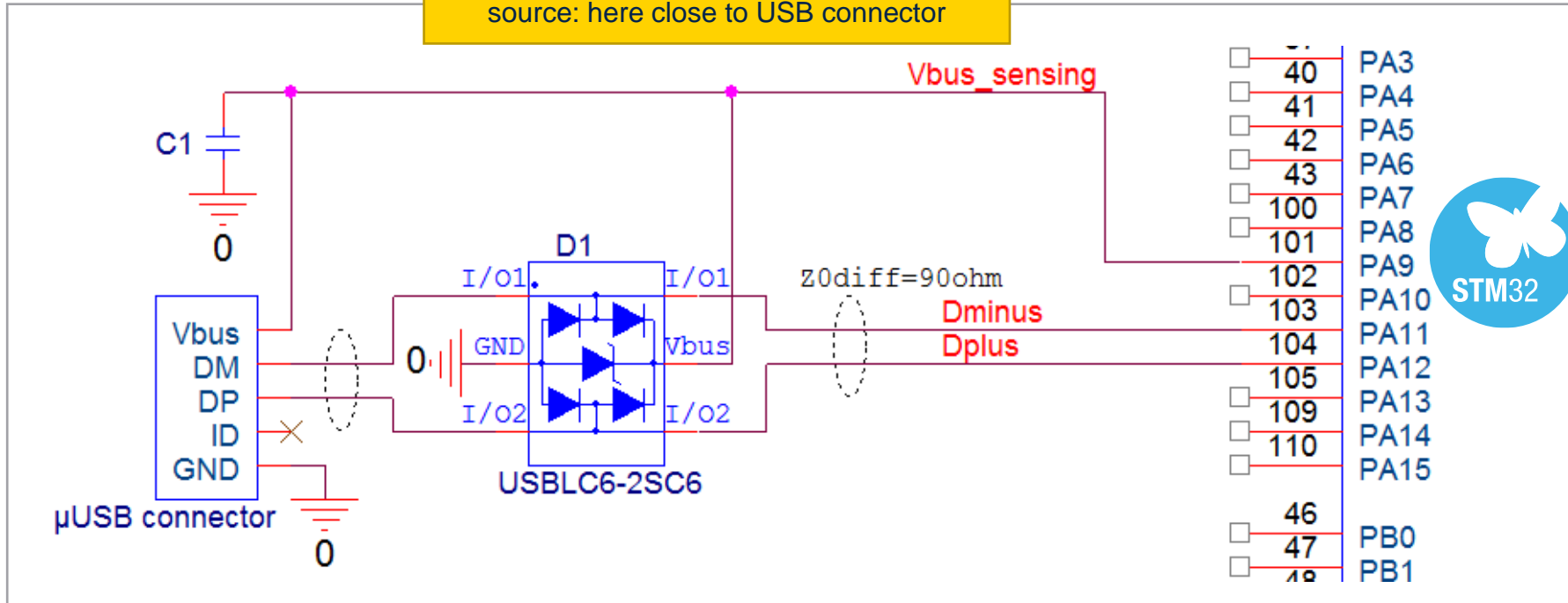




Usb 2.0 full speed without OTG



DESIGN TIP:
Place the ESD protection close to ESD source: here close to USB connector



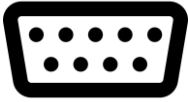
Reuse gerber file
STM32L4R9I-EVAL

USBLC6-2SC6



SOD323-6L

- Compliant with USB 2.0 eye diagram
- ESD robustness: ± 15 kV contact discharge IEC61000-4-2

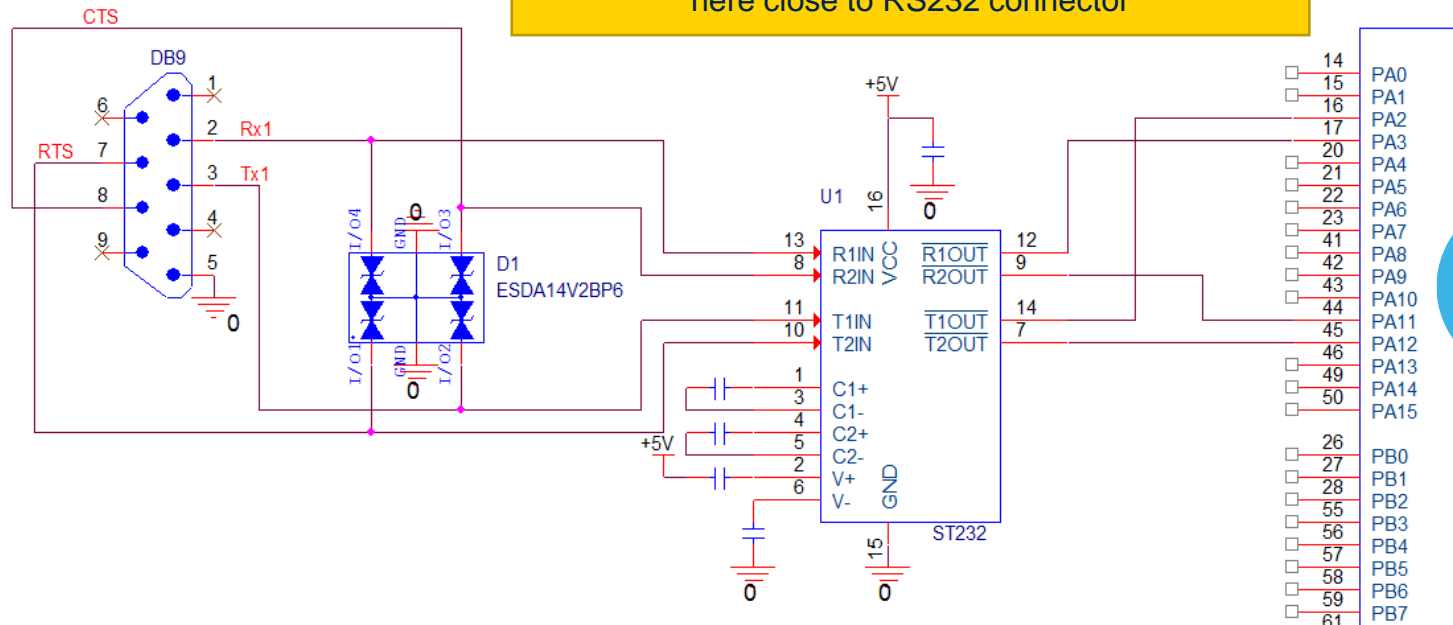


RS232



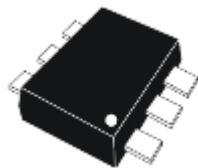
DESIGN TIP:

Place the ESD protection close to ESD source:
here close to RS232 connector



Reuse gerber file
STM32L4R9I-EVAL

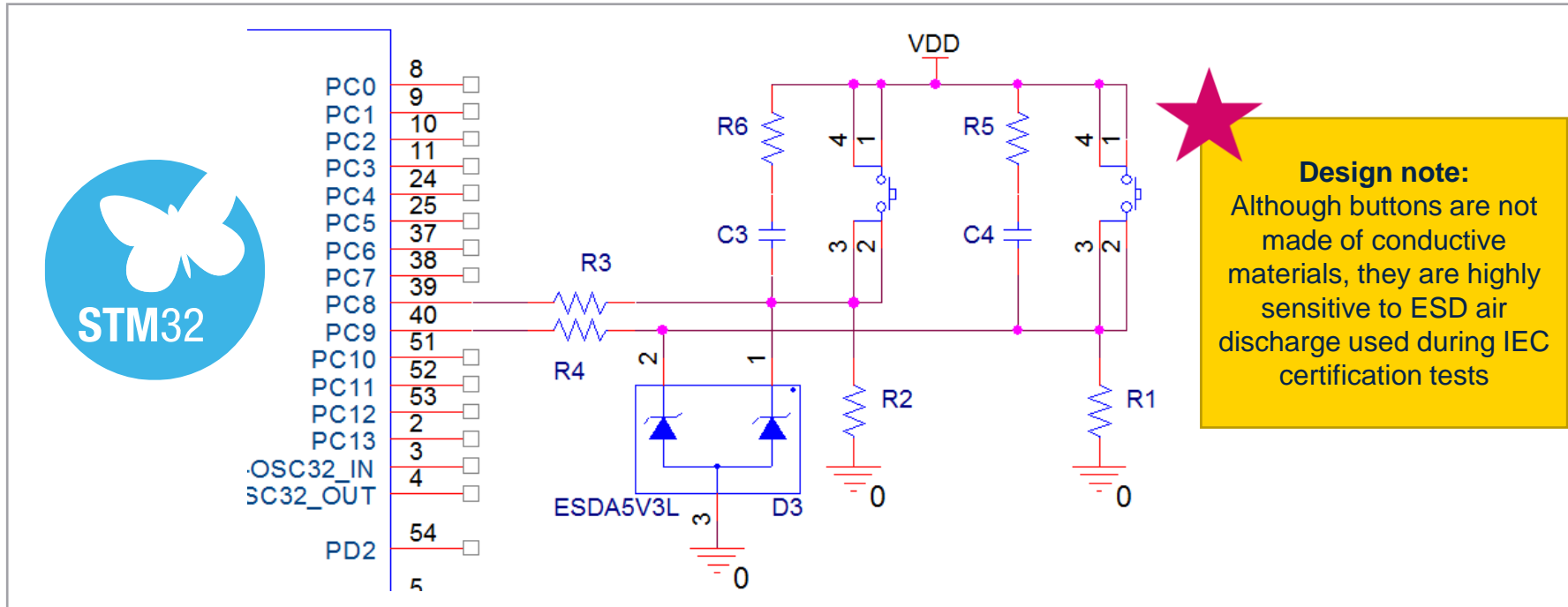
ESDA14V2BP6



SOT666-6L

- Low capacitance, 4-line, bi-directional ESD protection
- ESD protection as per IEC61000-4-2 Level 4: $\pm 8\text{kV}$ contact

User button MCU GPIO input



Reuse gerber file
STM32L4R9I-EVAL



ESDA5V3L



SOT23-3L

- PCB space saving: 2 diodes array
- ESD robustness: ± 30 kV contact discharge IEC61000-4-2

STM32MP1-DK2 discovery

ESD protections and filters

MORPHO CONNECTOR
ESDA7P120-1U1M




5V Vin

MICRO SD CARD
HSP051-4M10 (x2)




SDMMC dataline

USB Type-C Power Delivery
ESDA7P120-1U1M, ESDA25L

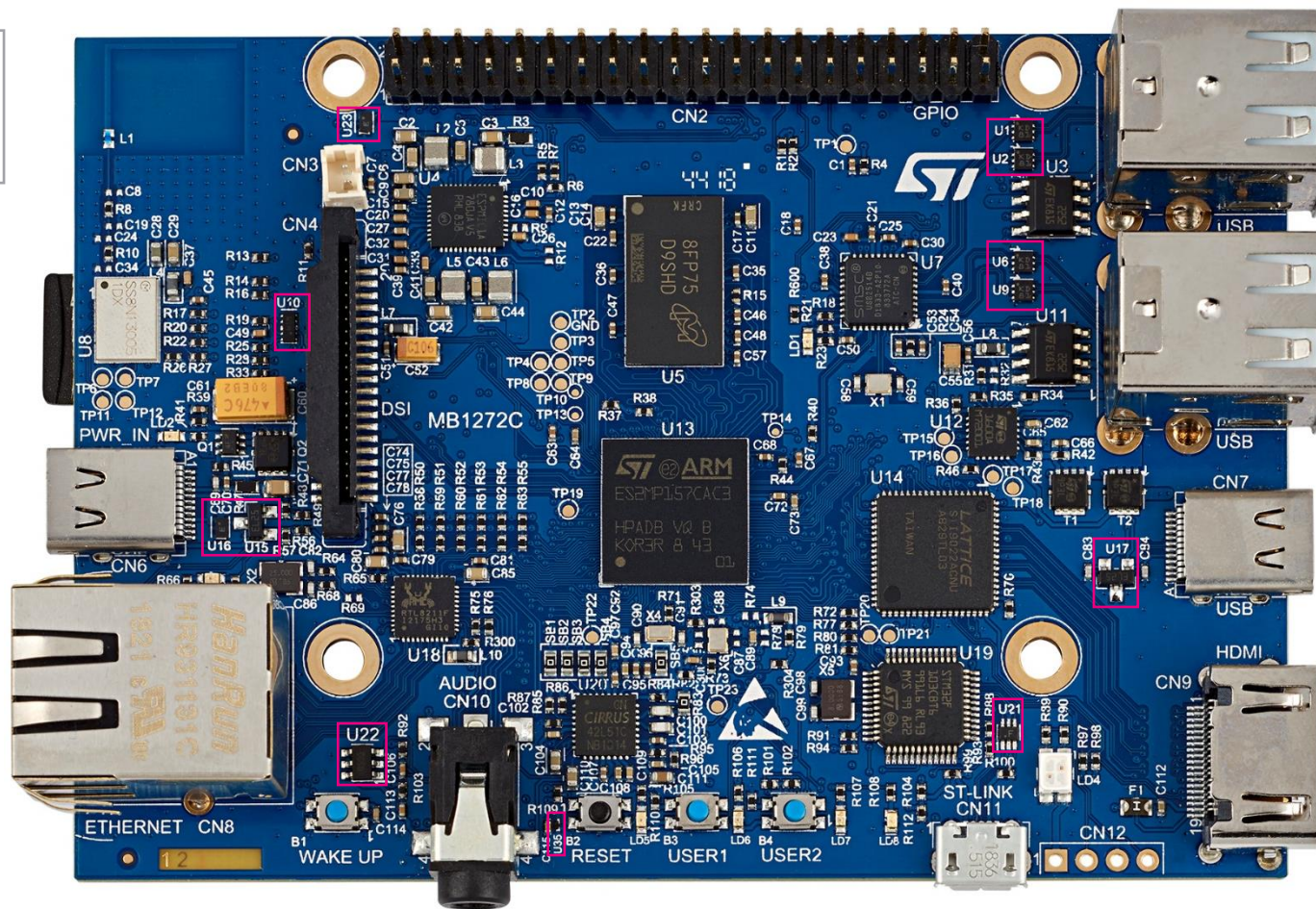







VBUS CC1, CC2

ETHERNET
HSP053-4M5






USB HOST x2 (Dual USB Type-A)
ESDA7P120-1U1M (x2), ECMF02-2AMX6 (x2)

VBUS DP, DM

USB HOST x2 (Dual USB Type-A)
ESDA7P120-1U1M (x2), ECMF02-2AMX6 (x2)





VBUS DP, DM

USB Type-C DRP (Source Only)
ESDA7P120-1U1M, ESDA25L, ECMF02-2AMX6







VBUS CC1, CC2 DP, DM

HDMI
ECMF04-4HSWM10 (x2), ESDALC6V1-5M6





TMDs datalines CEC, I2C, HPD

AUDIO
ESDA6V1BC6: 4-line ESD protection





OUTA, OUTB, MIC IN

USER BUTTONS
ESDALC6V1-1U2




ST-LINK USB CONNECTOR
USBL6-2P6



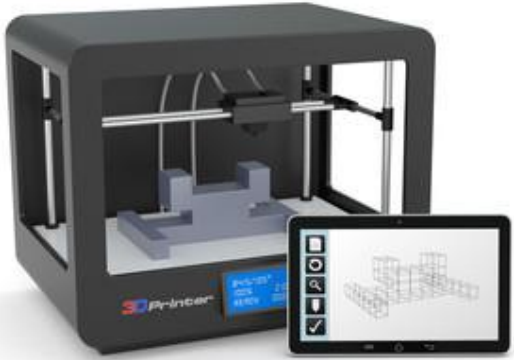

DP, DM, VBUS



STM32MP1

Electronic boards must be protected

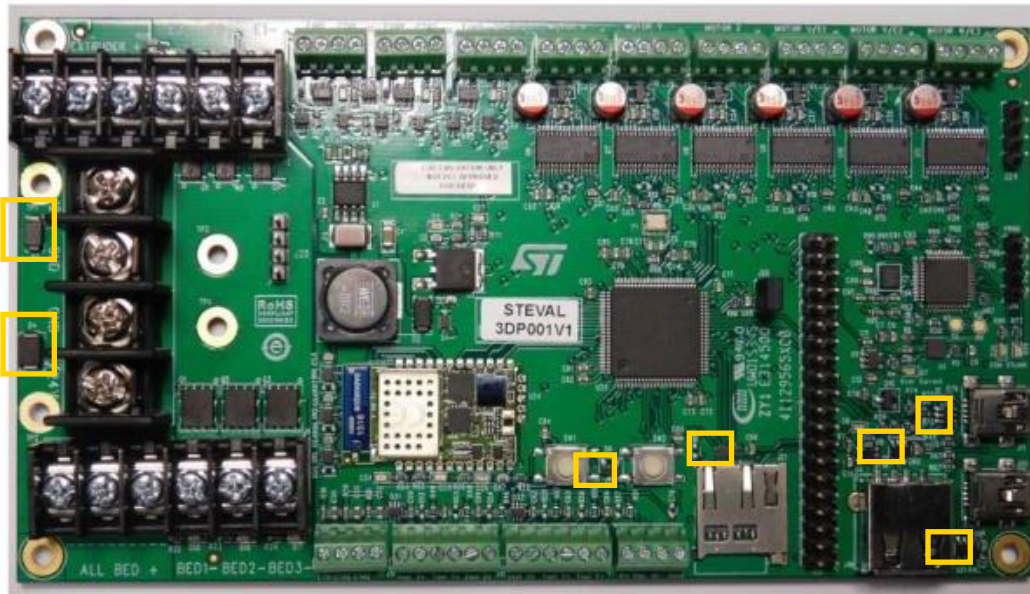
3D printer control board



SMAJ12A

SMBJ24A

EMIF06-MSD02N16



ESDA5V3L

3x USBLC6-2SC6

- Protections on the application PCB
 - Power lines → surge protection : IEC 61000-4-5
 - Connector
 - Button
 - SD card
- Integrated on all ICs → ESD protection for manufacturing is JEDEC HBM

ESD protections
for system:
IEC 61000-4-2

Resources

application notes and videos

- [AN5241](#), Fundamentals of ESD protection at system level
- [AN4871](#), USB Type-C protection and filtering
- [AN5121](#), HDMI ESD protection and signal conditioning products for STBs
- [AN3353](#), IEC 61000-4-2 standard testing
- [AN2689](#), Protection of automotive electronics from electrical hazards, guidelines for design and component selection
- [AN1826](#), TRANSIENT PROTECTION SOLUTIONS: Transil™ diode versus Varistor
- [AN5241](#) : Fundamentals of ESD Protection
- [Video](#) - ESD Protection: why and how to protect microcontrollers efficiently

ST protection finder mobile app

- ST PROTECTION FINDER is an application available for Android™ and iOS™ that allows you to explore ST's TVS product portfolio.
 - Parametric or series search engine
 - Efficient part number search engine




下载 APK 文件



4 steps to discover ST's portfolio


1 - OPEN application

ST Protection Finder (1.0.1 ML off) 

 PART NUMBER SEARCH

 ESD Protection
(IEC61000-4-2)

 TVS clamping diodes
(10/1000 μ s and 8/20 μ s)

 Current-Limiting Termination
for Programmable Logic Controller

 MY FAVORITES

2-SELECT parameter

 ST Parametric Search 

ESD Protection
(IEC61000-4-2)

Stand off Voltage



Breakdown voltage



Line Capacitance I/O-GND




Number of protected Line

3- CHOOSE product

 ST 20/30 Product

DVIULC6-4SC6Y

Active

 ESD Protection

V_{RM} Typ
5 V

V_{BR} Min
6 V

C_{LINE} Typ
0.85 pF


Nb of Line
4

Directionality
UNI-DIRECTIONAL

Package SOT23-6L

EMIF02-02OABRY

Active

 ESD Protection

V_{RM} Typ
3 V

V_{BR} Min
6 V

C_{LINE} Typ
1.2 pF

Nb of Line
2

Directionality
BI-DIRECTIONAL

Package QFN-6L WF

4- GET datasheet

 EMIF02-02OABRY  

EMIF02-02OABRY

Active

 ESD Protection 

Key Features

- Attenuation profile compliant with BroadR Reach™ requirements from -40 °C to 125 °C
- Return loss (S_{dd11}) at 60 MHz
 - -20 dB
- Components matching
 - 1% (between line 1 and 2)
- Package
 - Dimensions: 3.0 x 3.0 mm
 - Pitch: 1.1 μ m
 - Wettable flank QFN
- AEC-Q101 compliant

Technical Documentation

Data Sheet

Description	Version	Size
 Data Sheet	1.0	1115 KB

Thank you

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